

Magneto-transport of electrons in near surface InAs quantum wells in contact with NbTiN

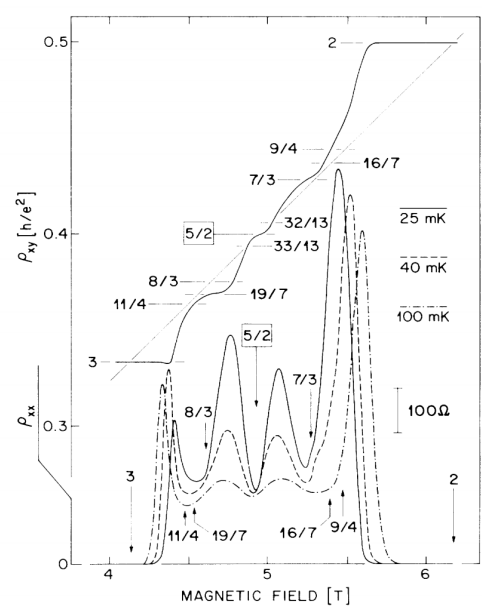
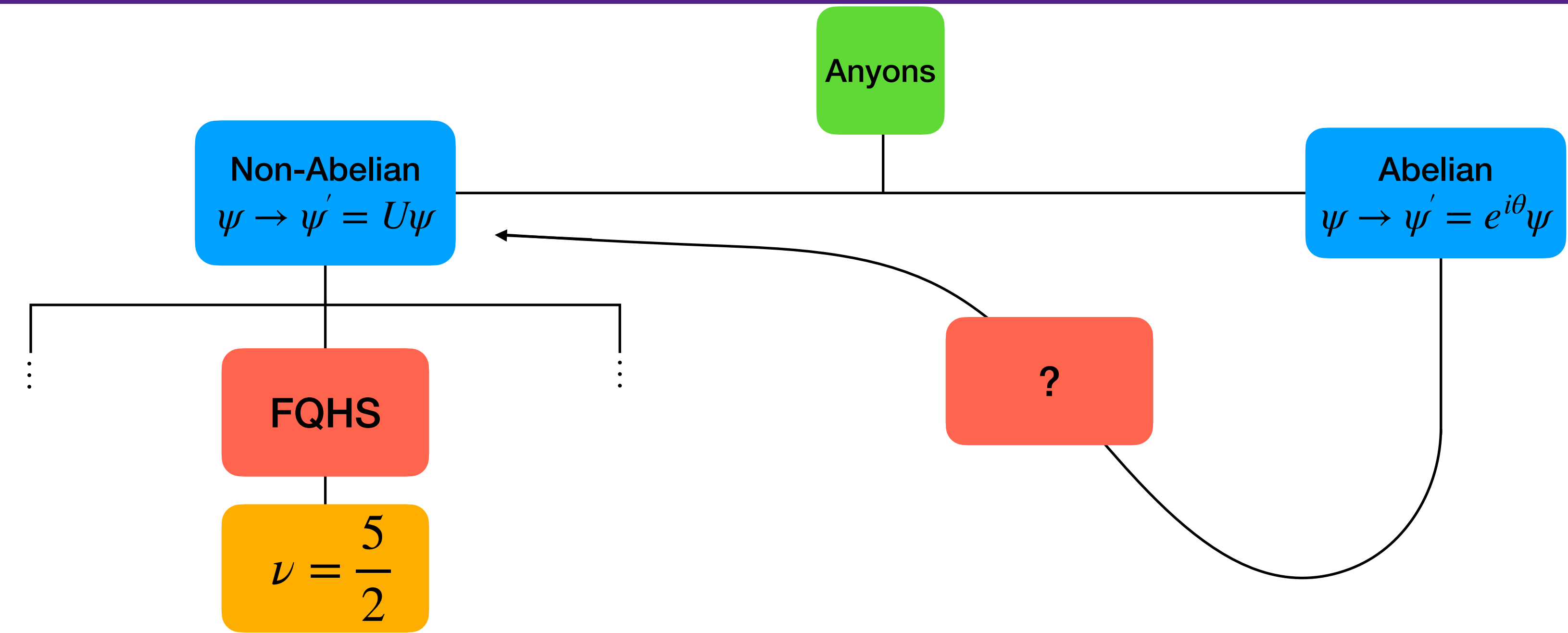
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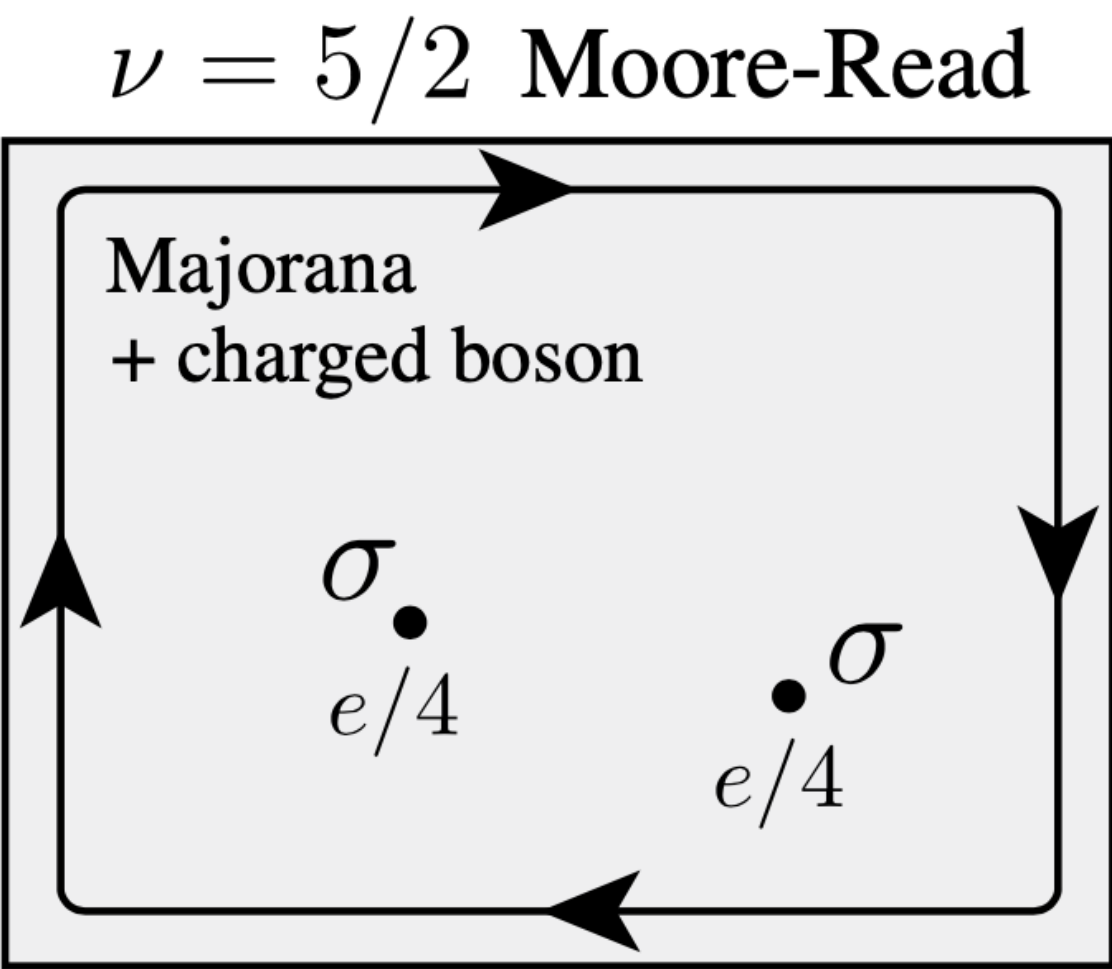
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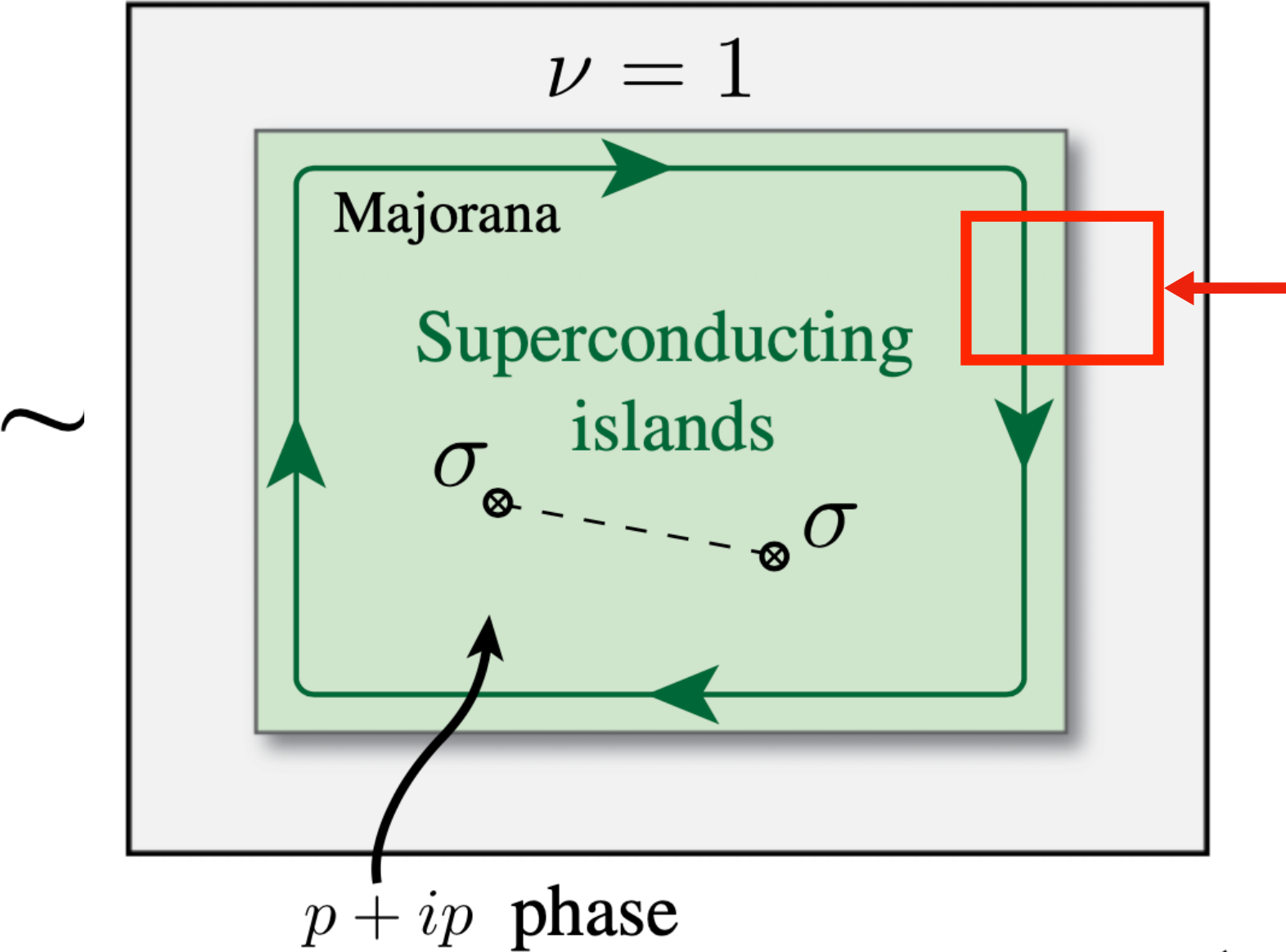
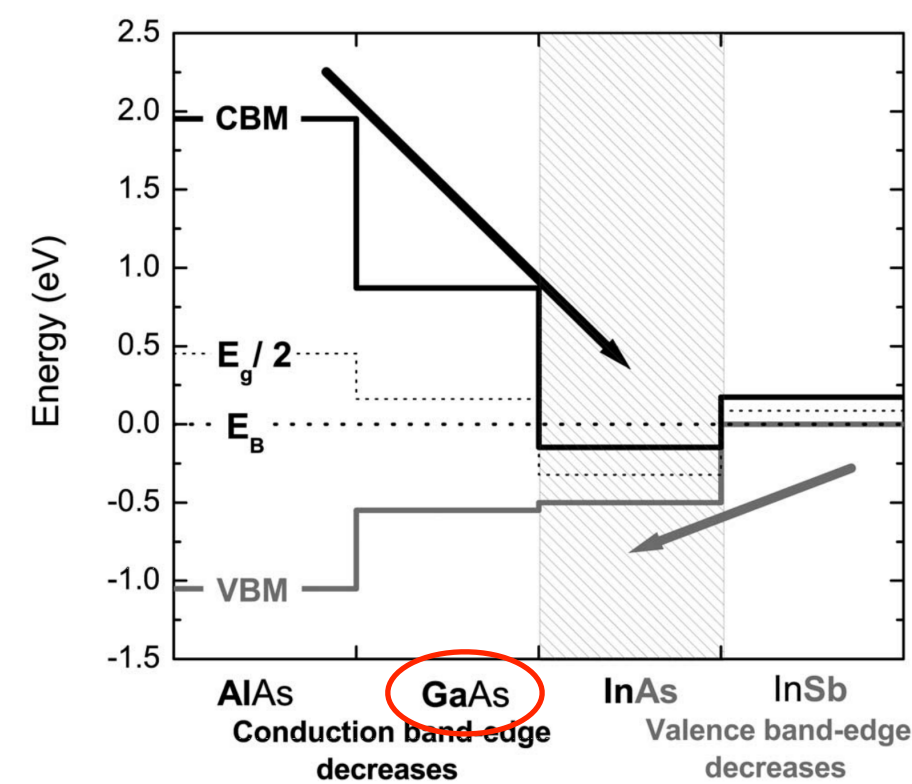
Website: <https://wp.nyu.edu/shabanilab/>



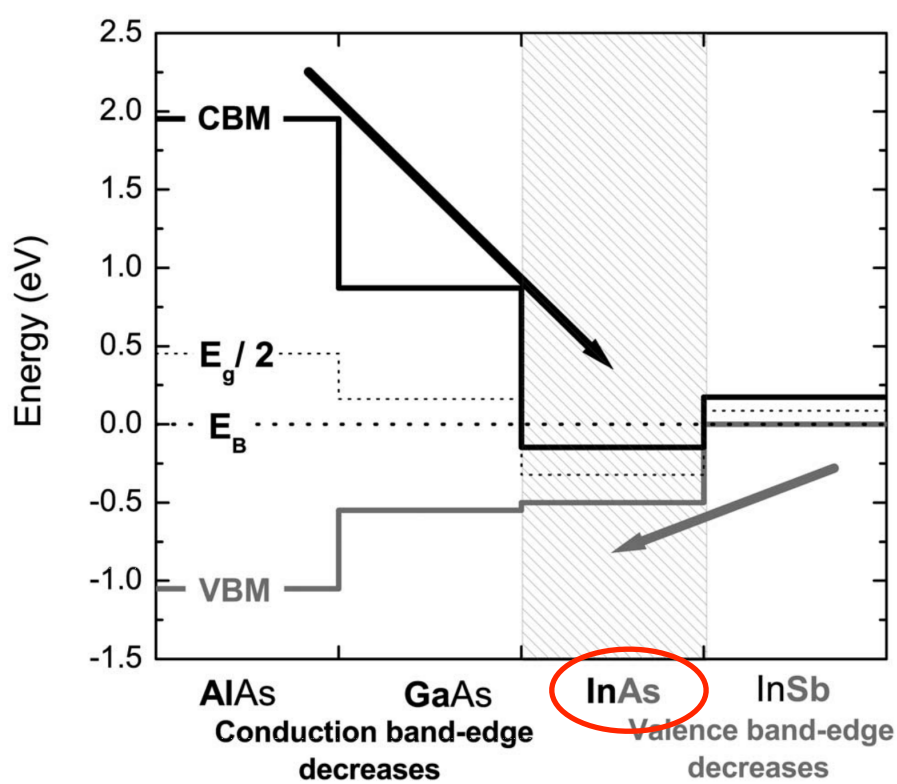


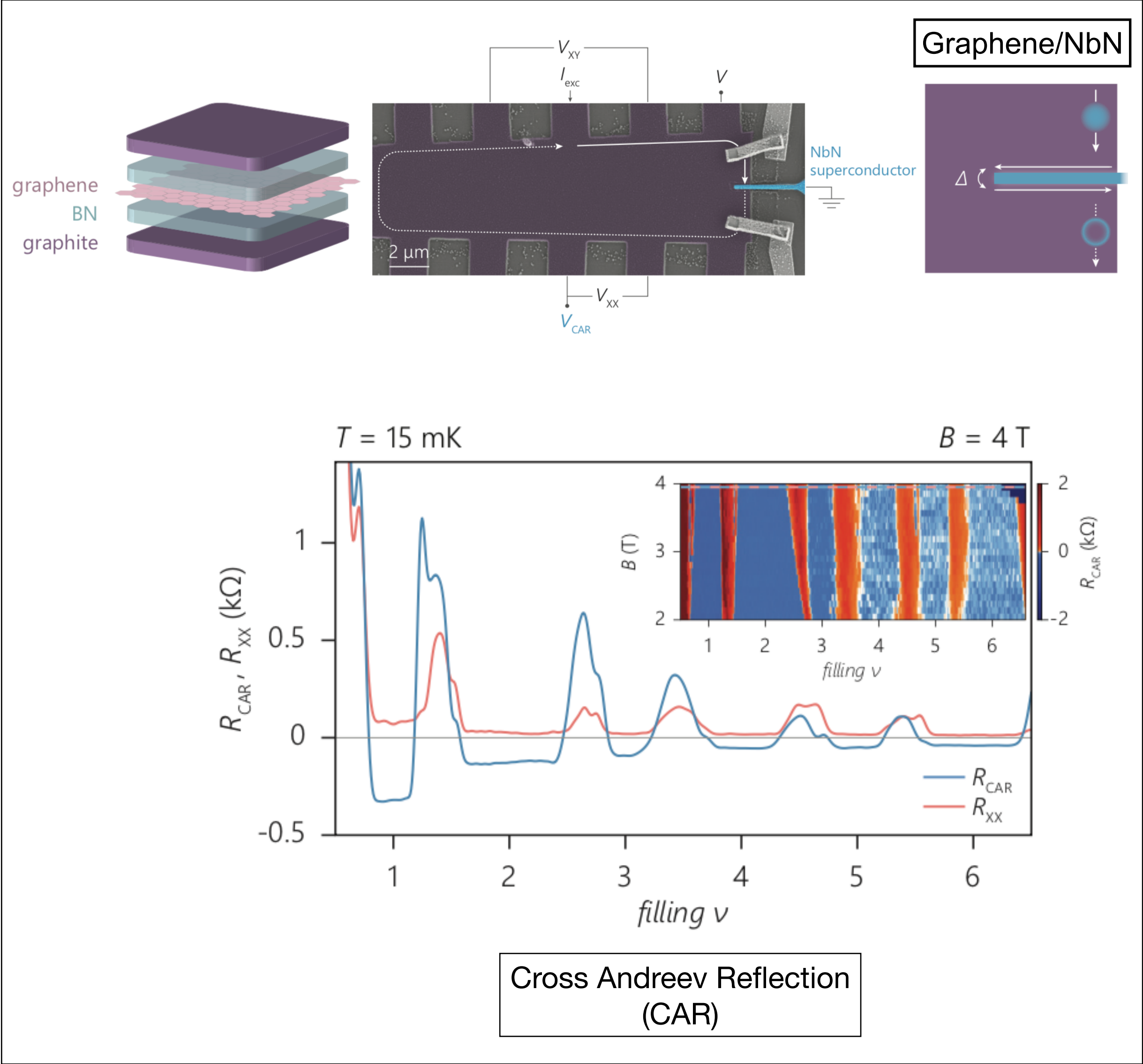
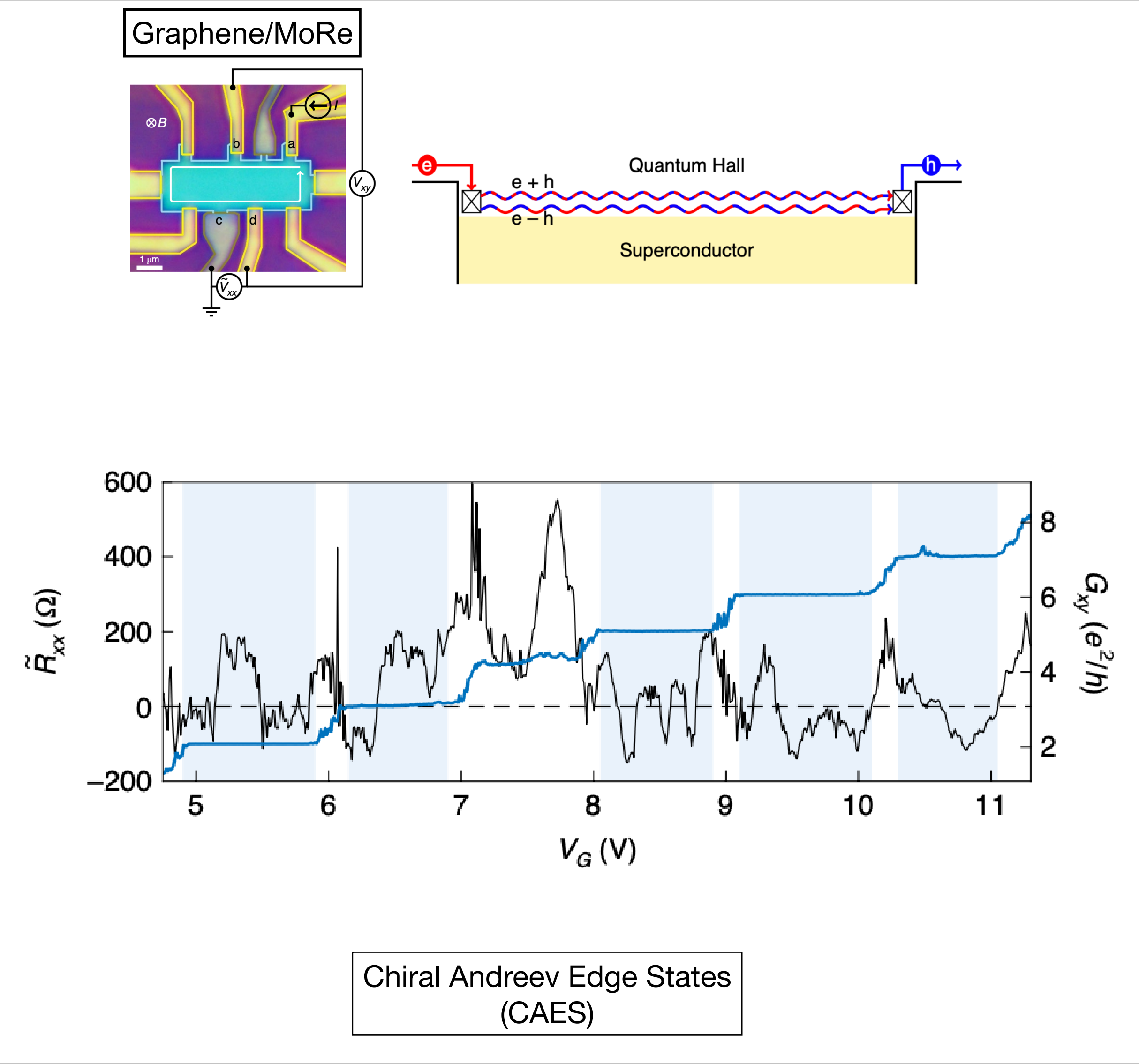


$$\mu = 30,000,000 \frac{cm^2}{Vs}$$

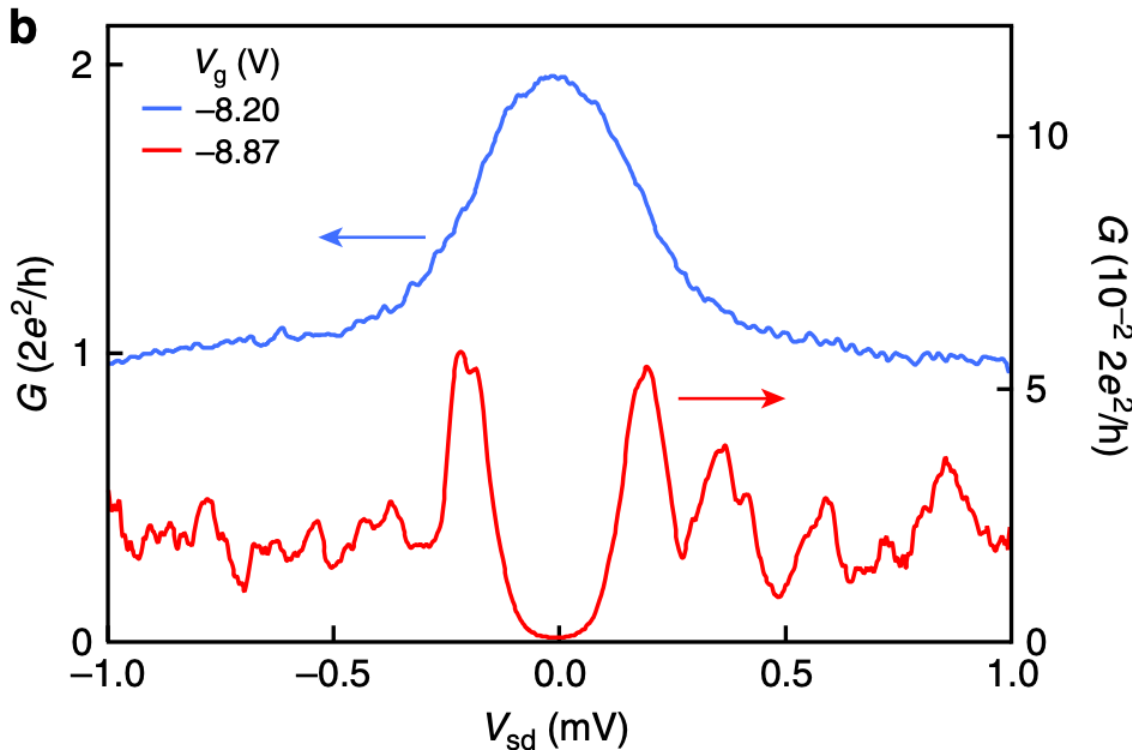
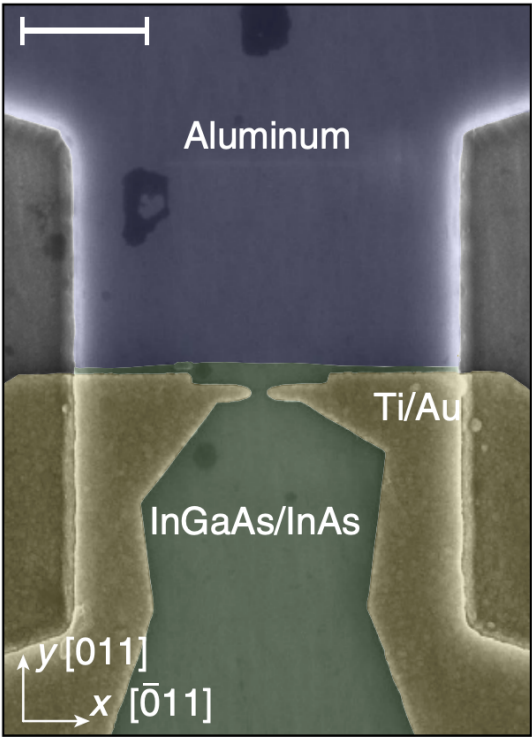
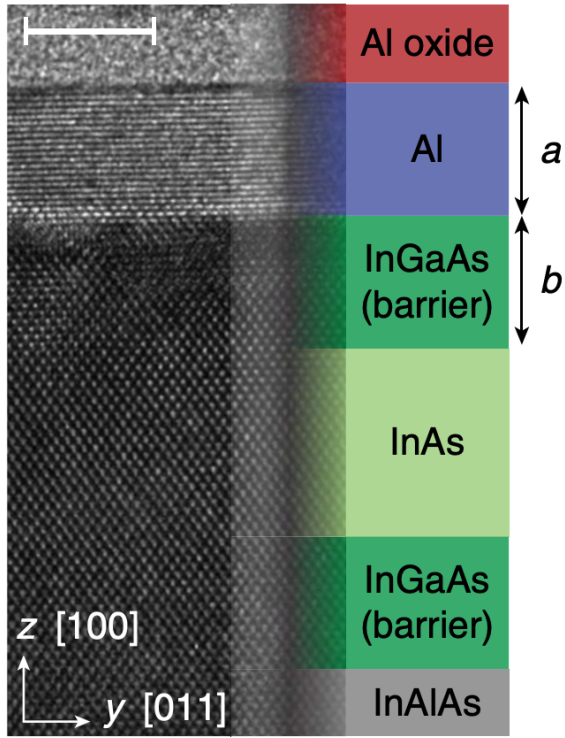
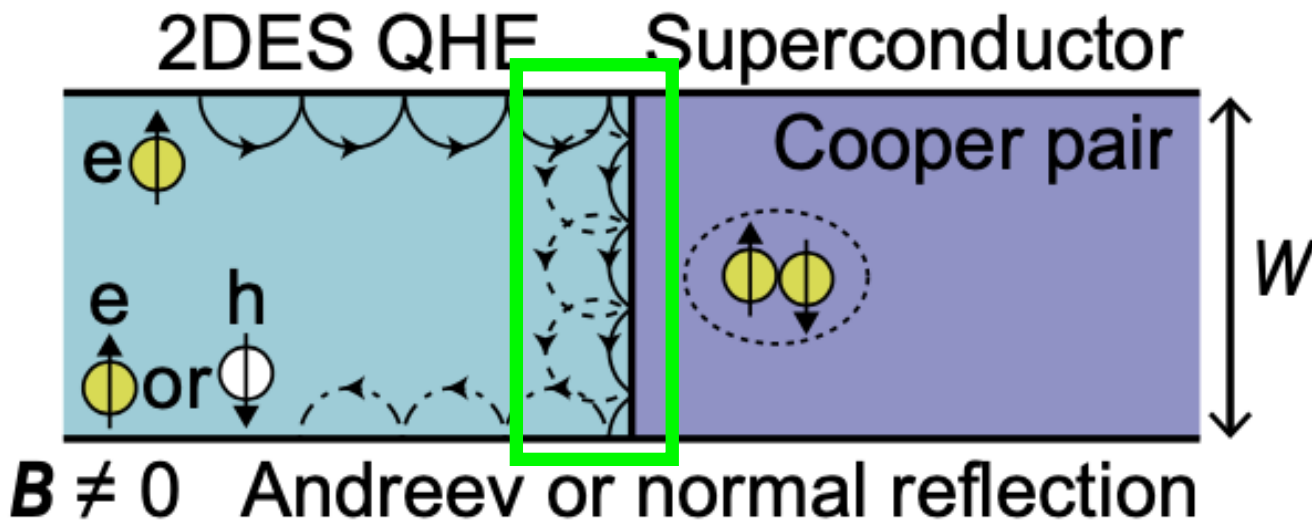
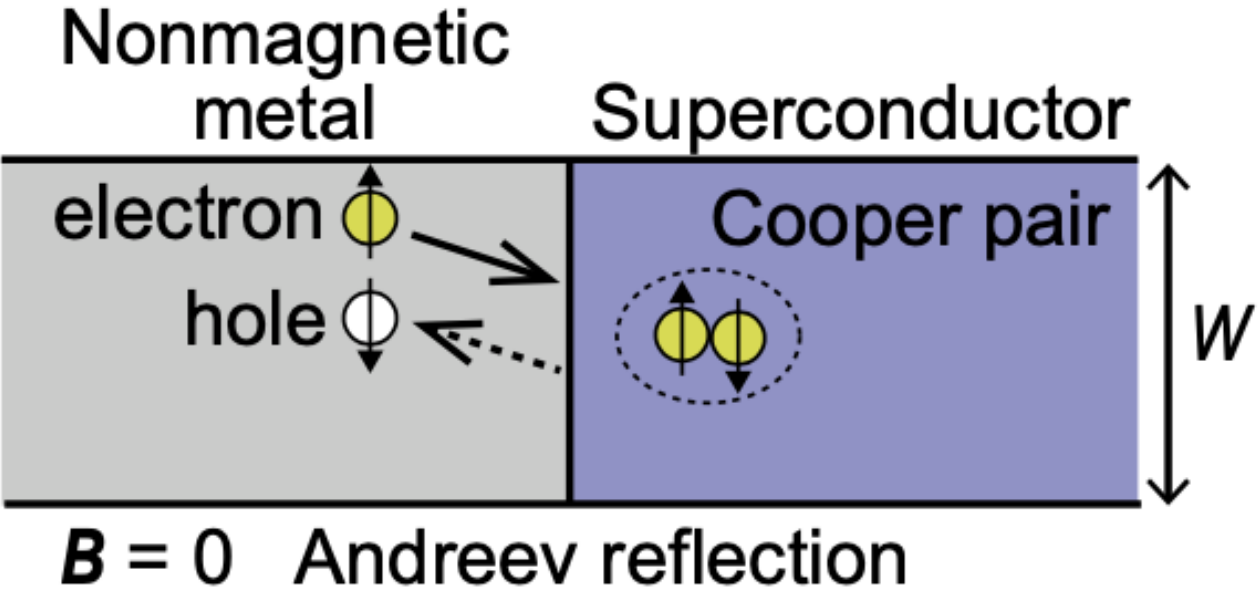


$$\mu \approx 10,000 \frac{cm^2}{Vs} , \nu = 1 + \text{Superconductivity}$$



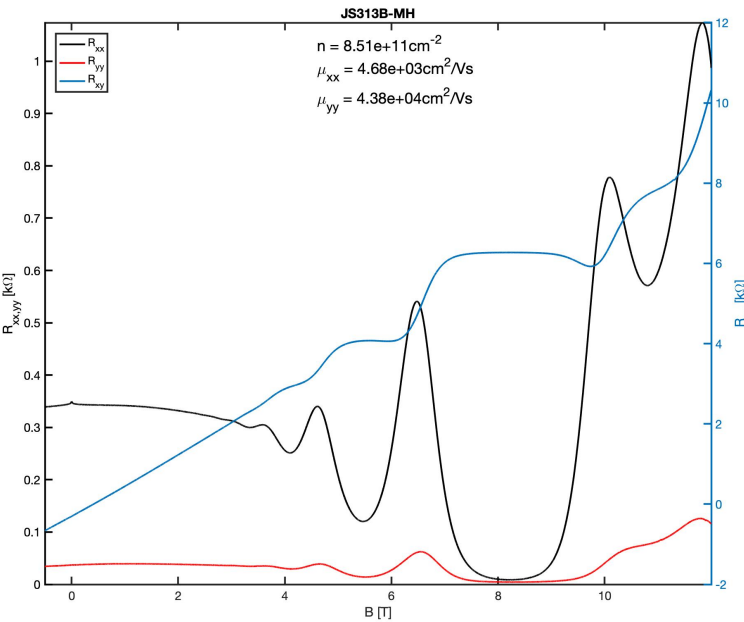
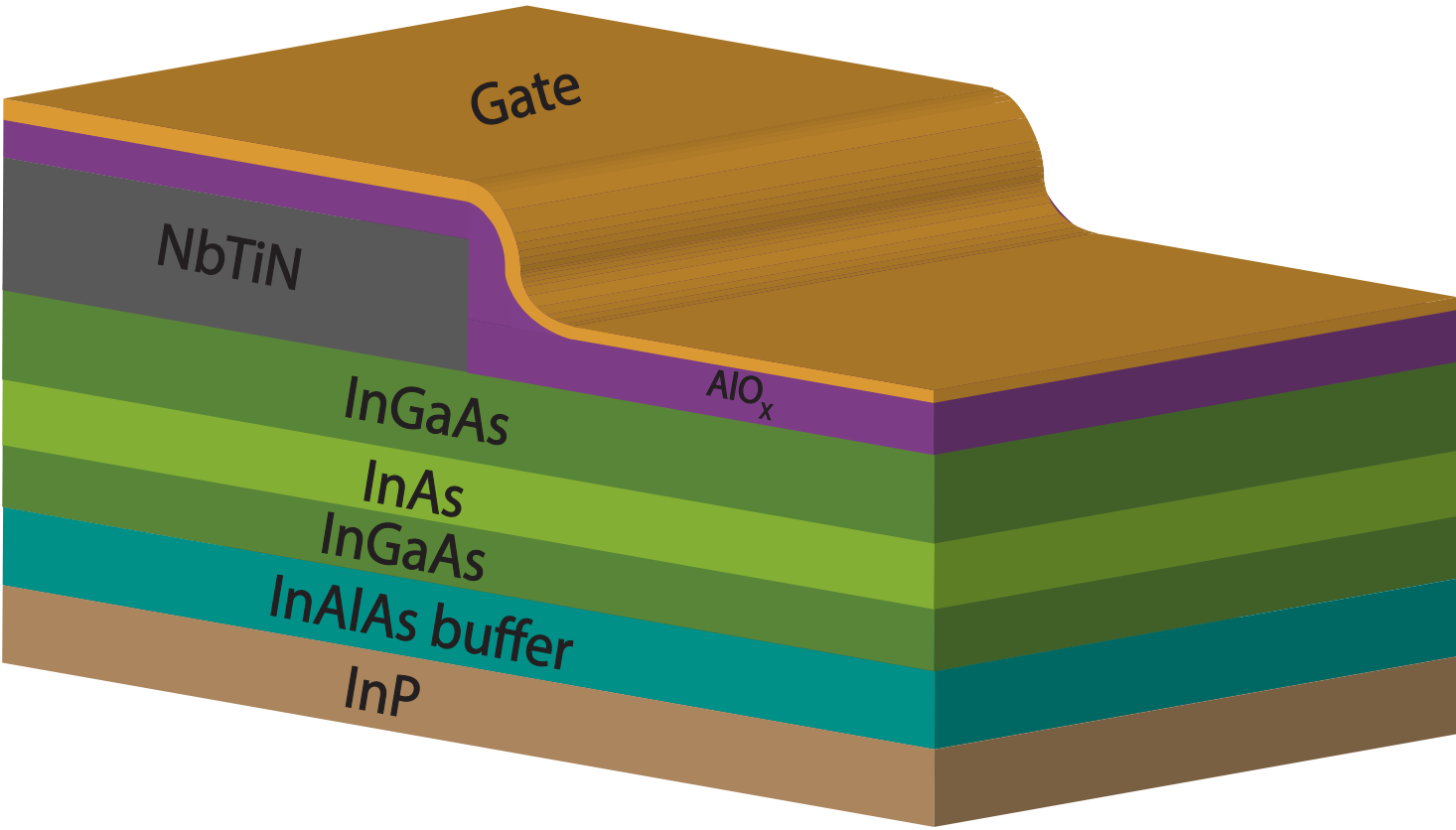
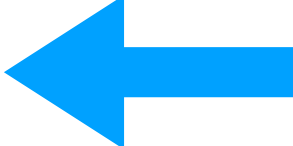
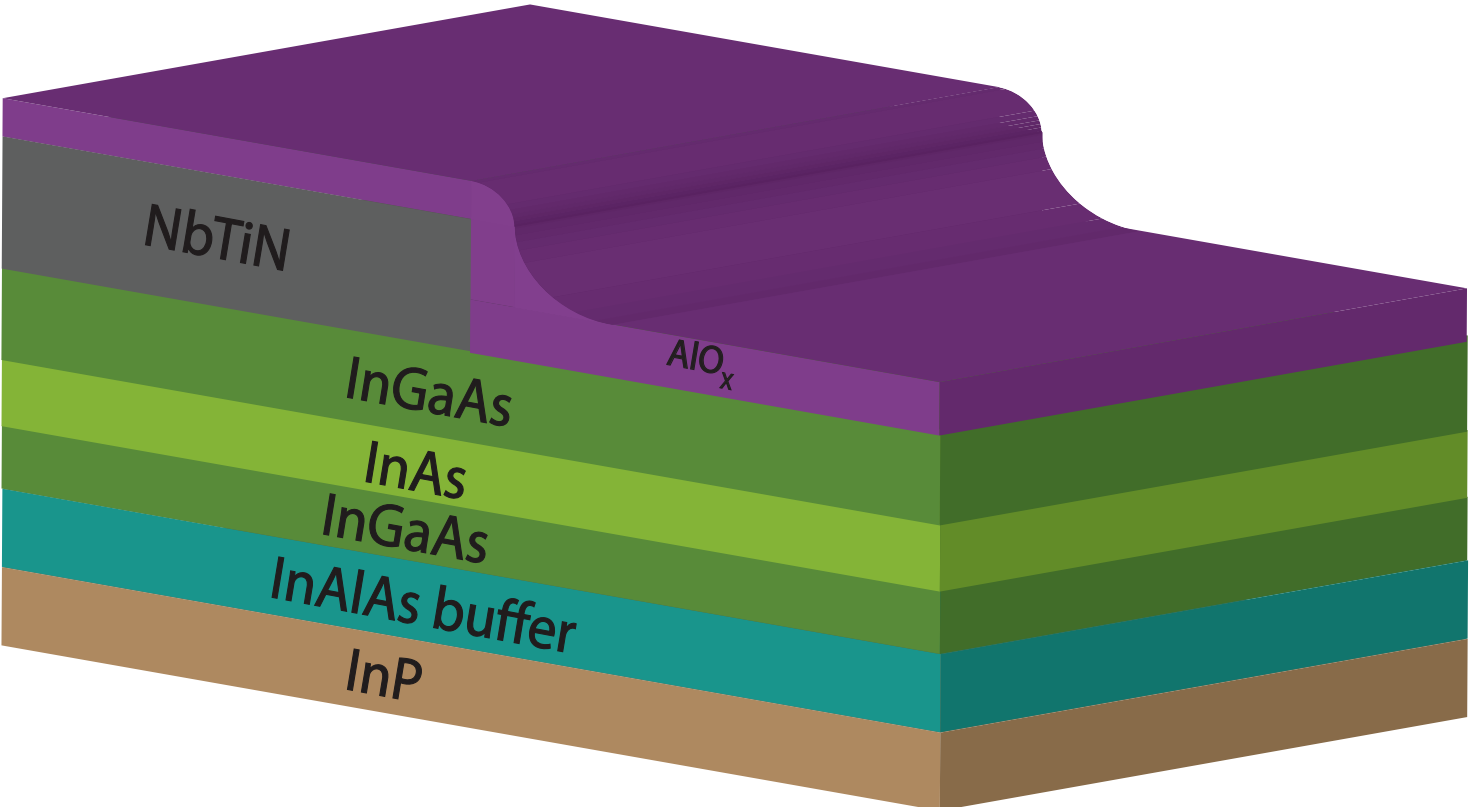
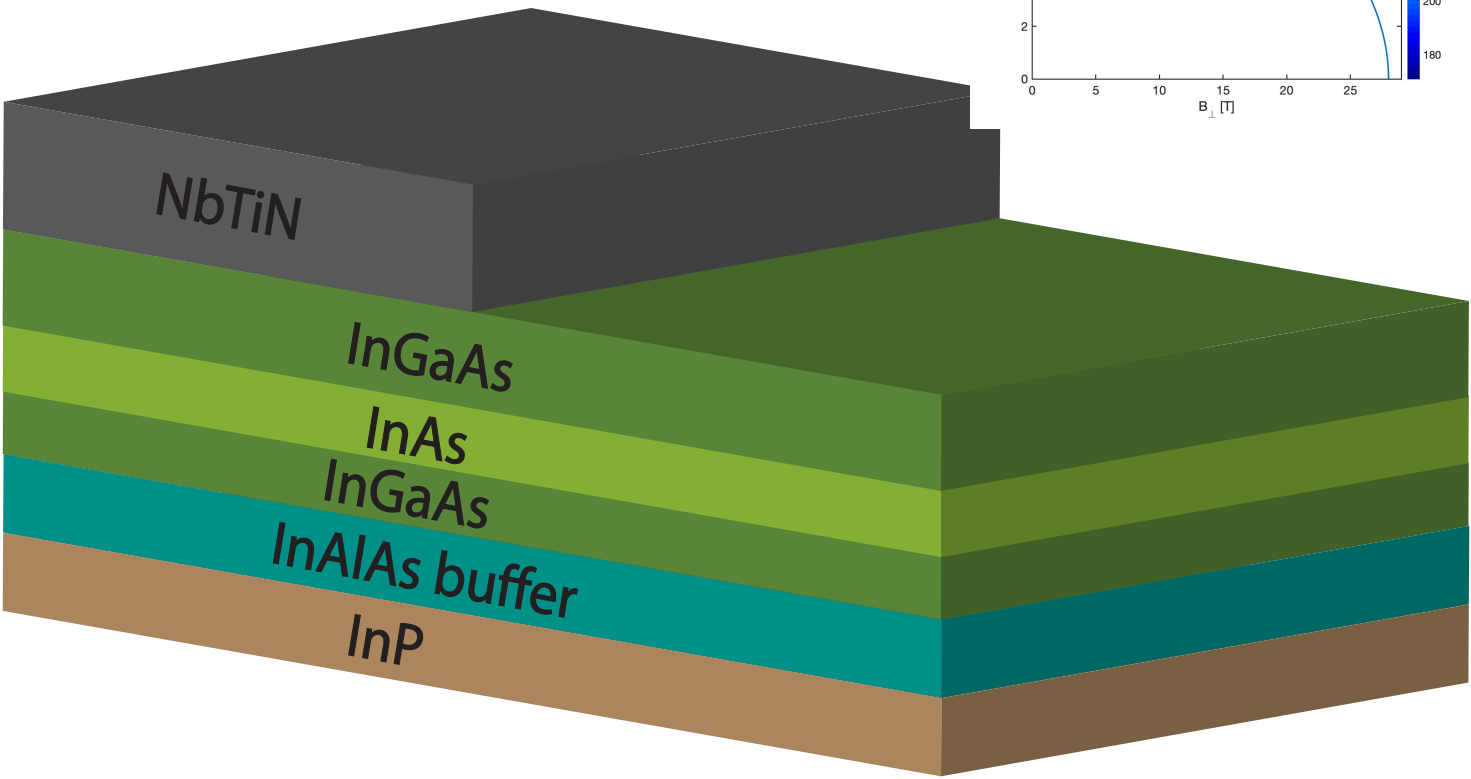
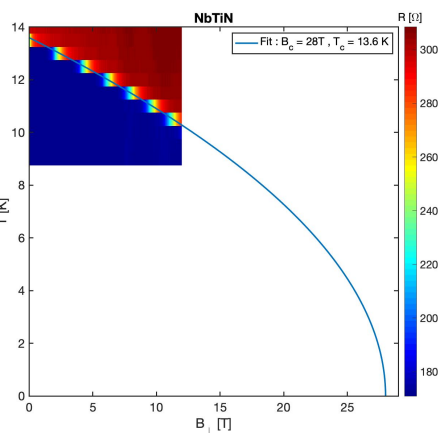
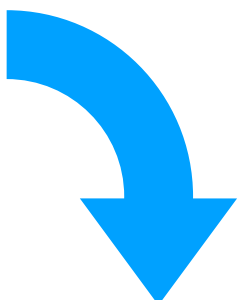
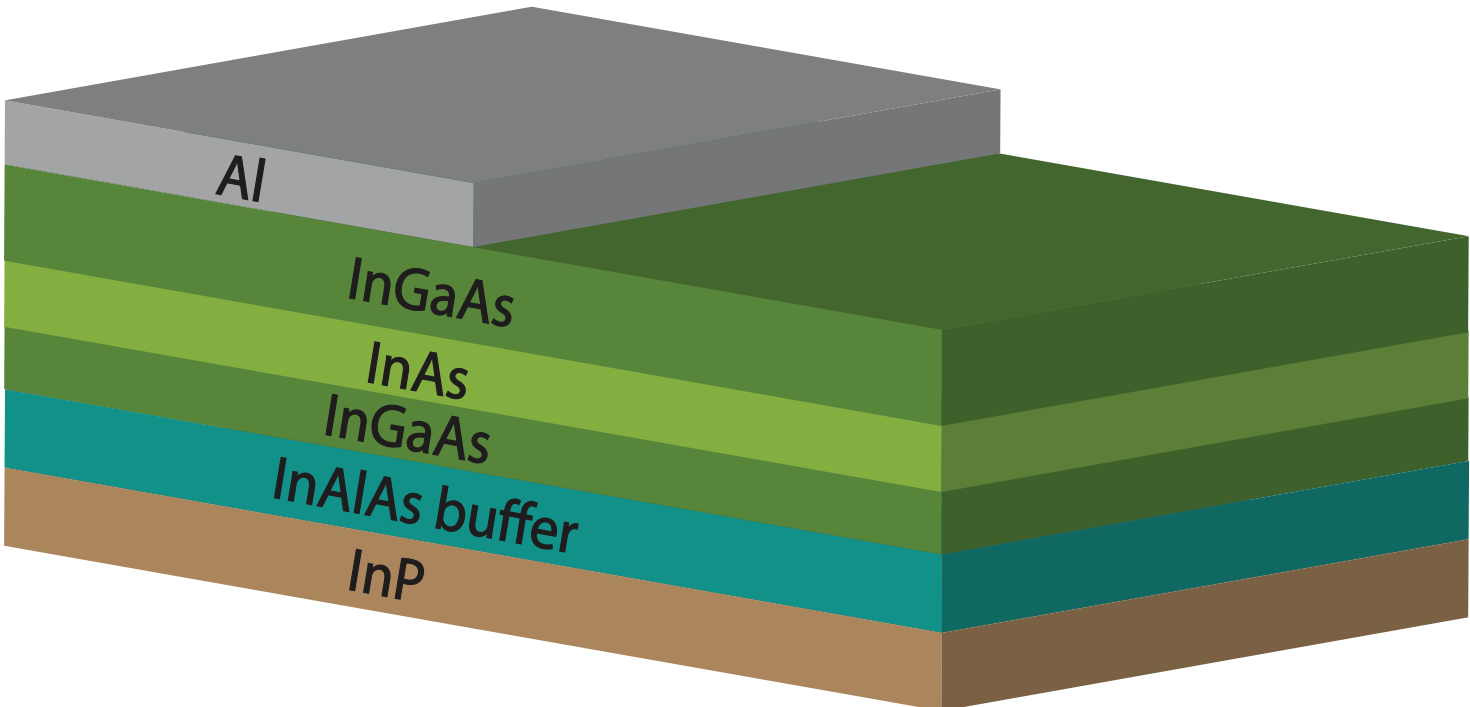
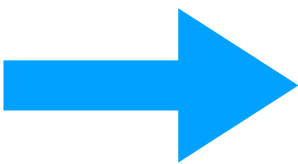
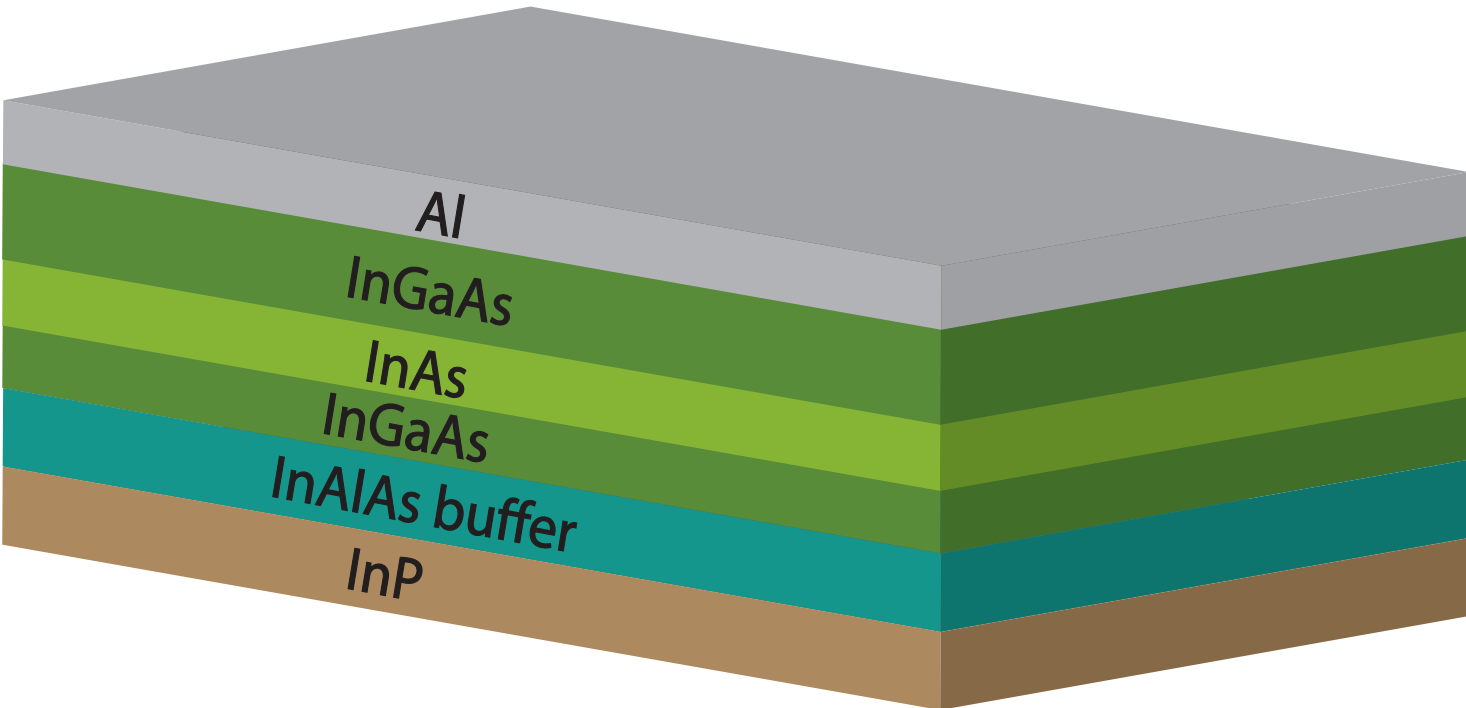


Andreev Reflection

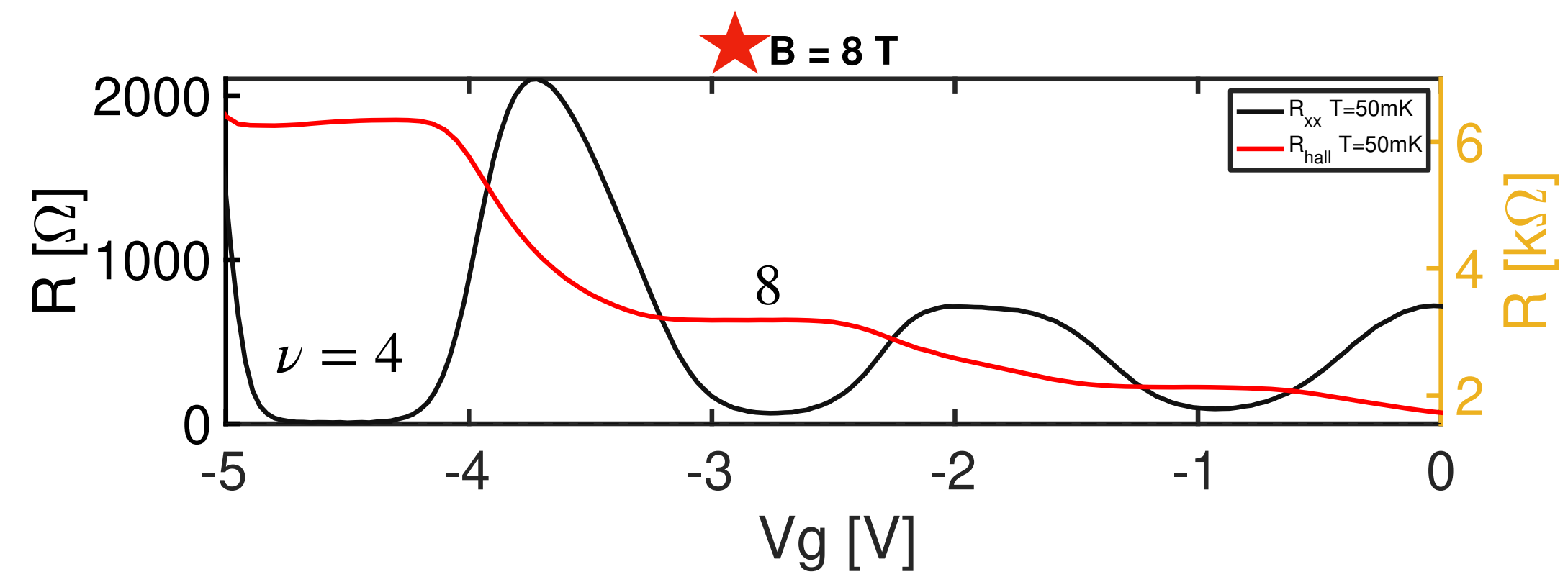
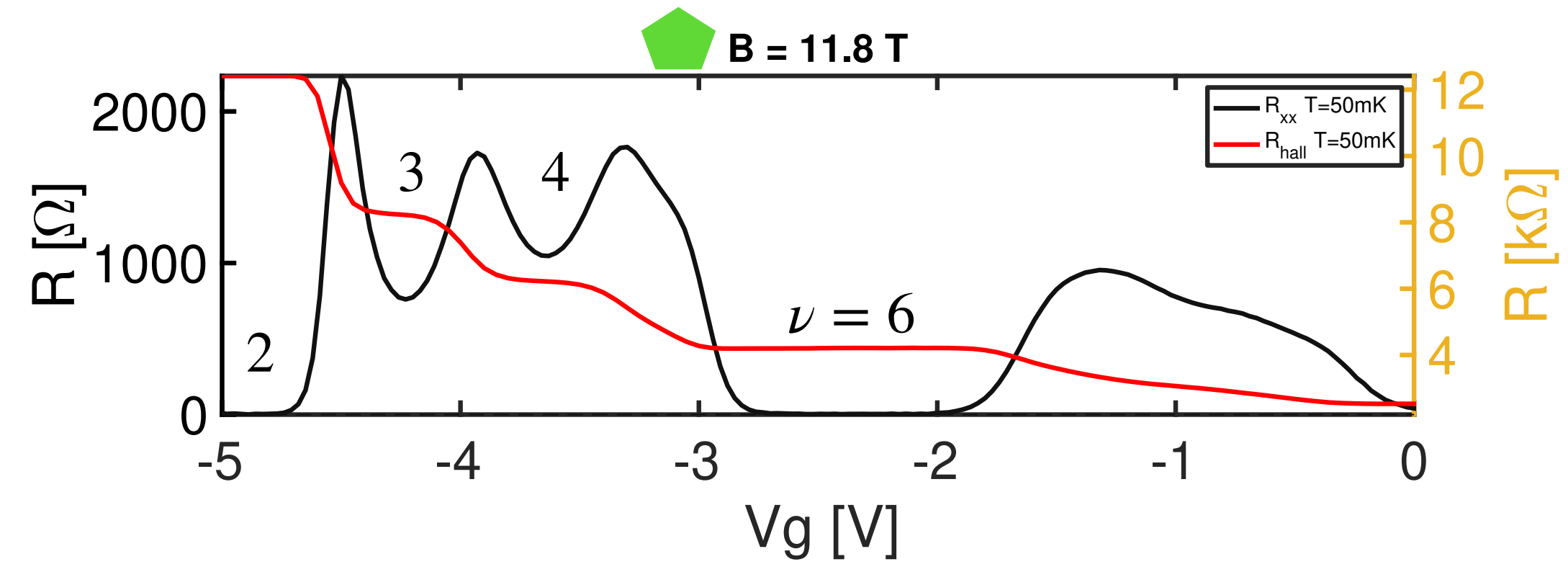
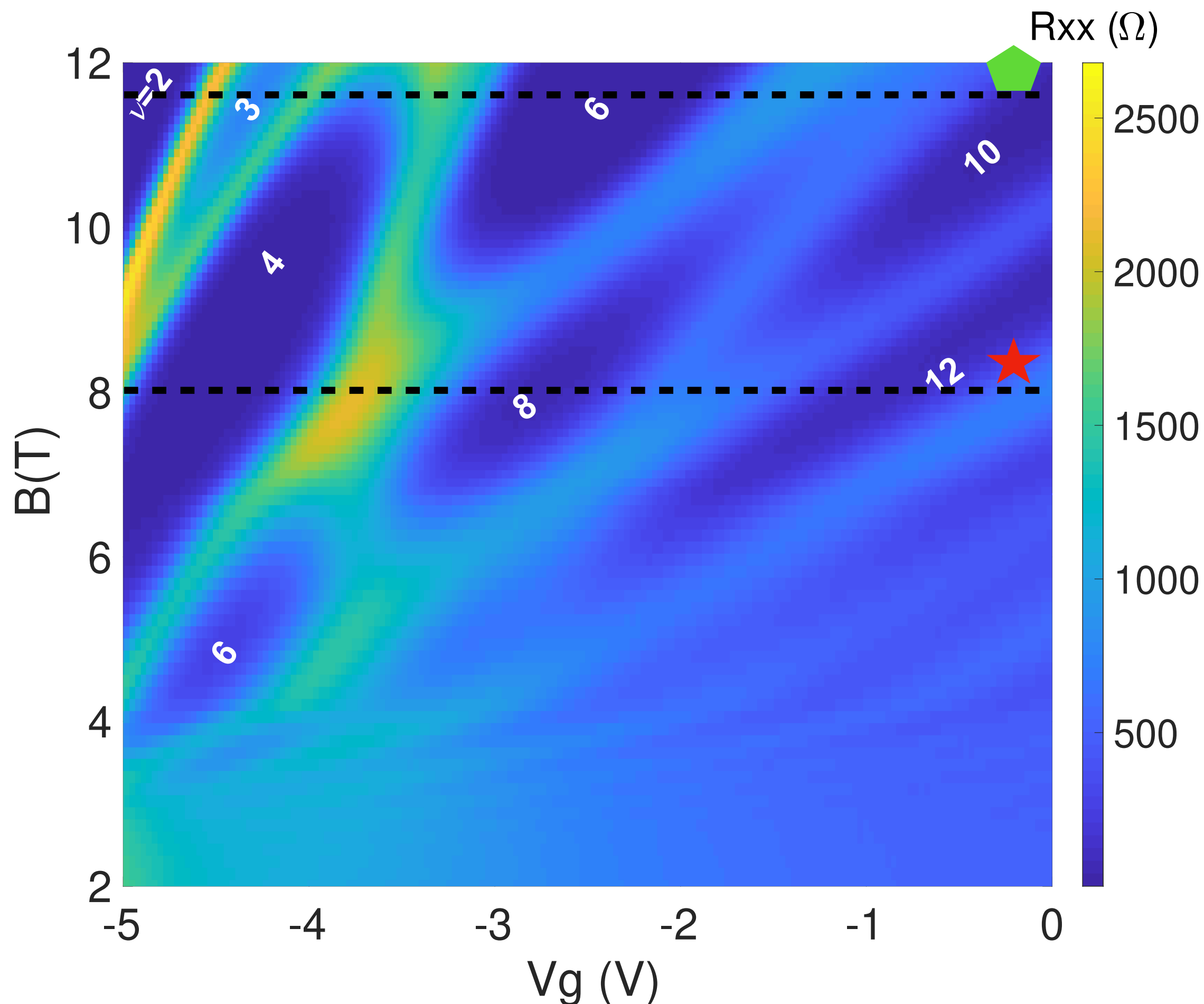
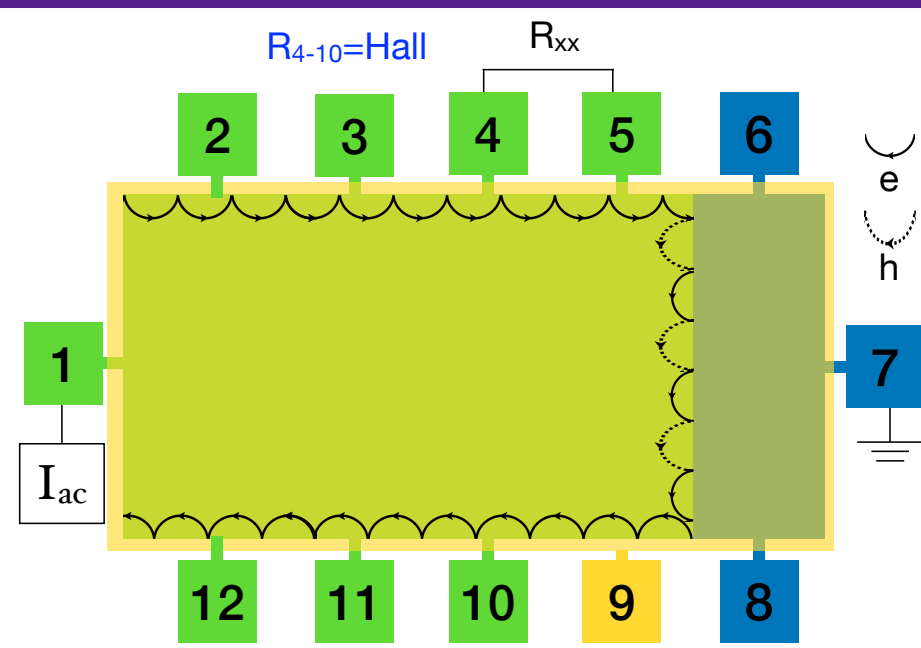


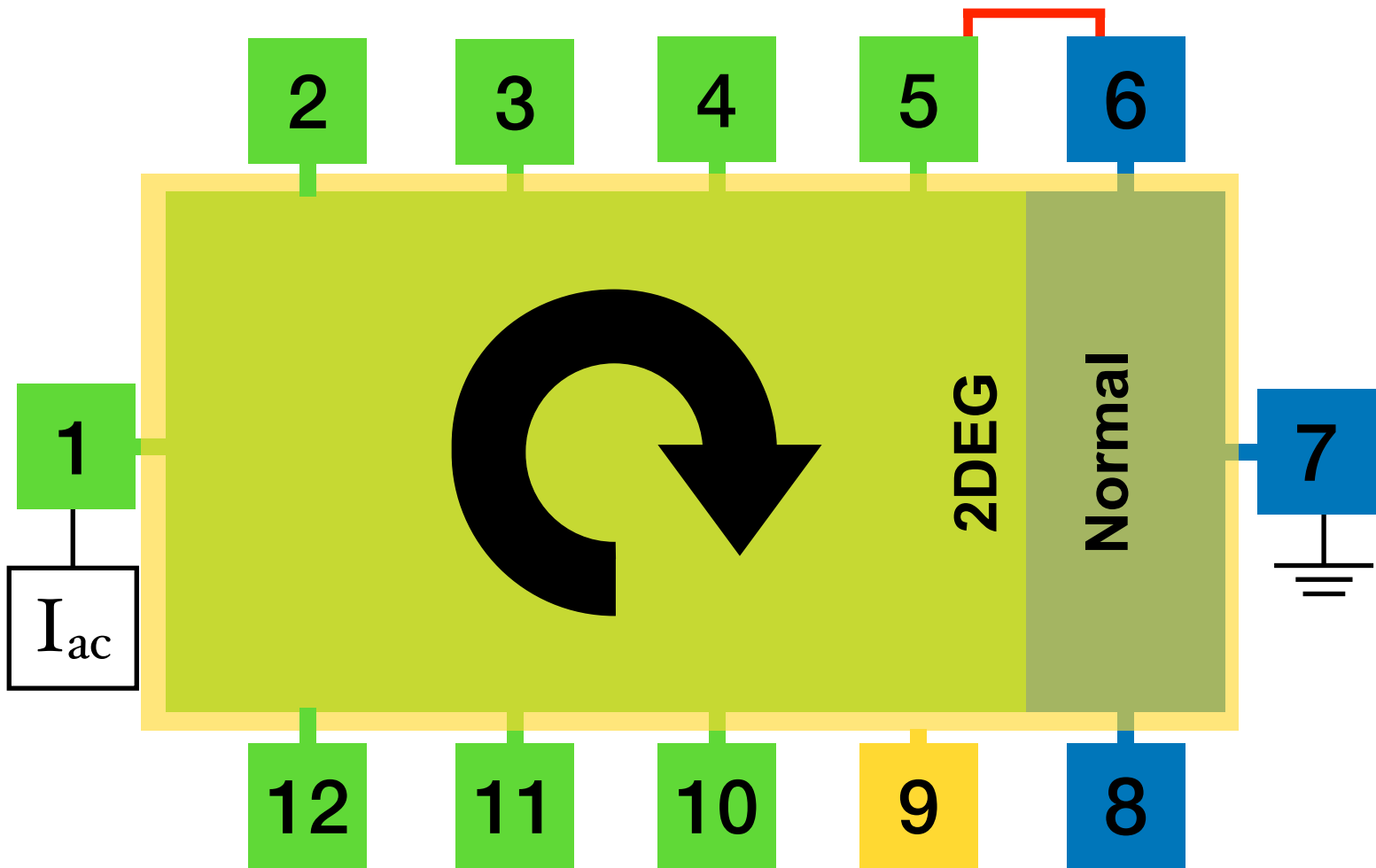
$$G_{ns} = 2G_0 \frac{G_{nn}^2}{(2G_0 - G_{nn})^2},$$

Focus of our study



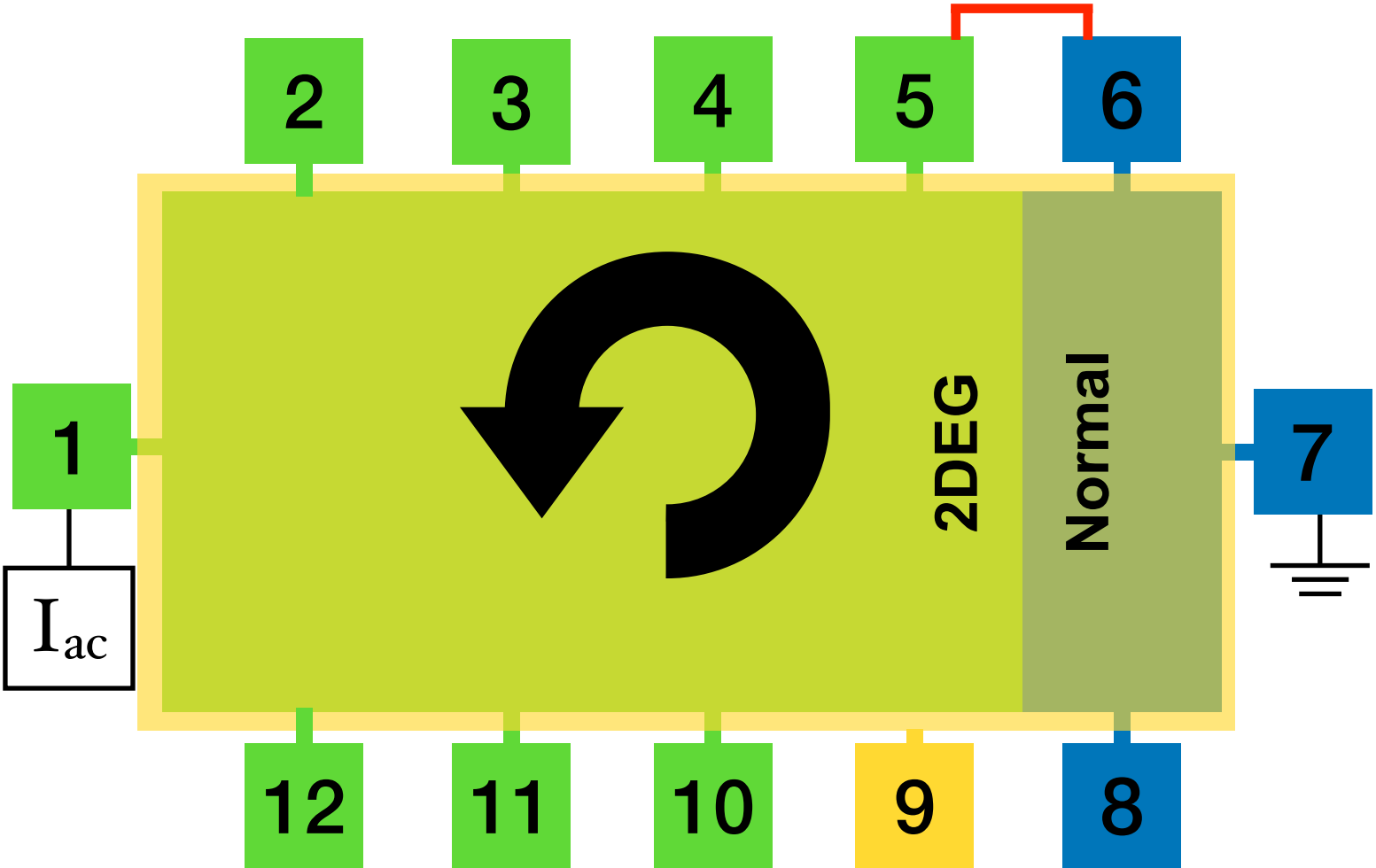
2DEG Characterization





$+B$

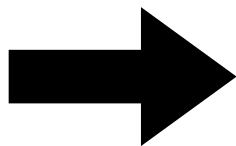
$$R_{5-6} = \frac{h}{e^2} \frac{R}{NT}$$



$-B$

$$R_{5-6} = \frac{h}{e^2} \frac{1}{NT}$$

Ideal interface:
R=0, T=1

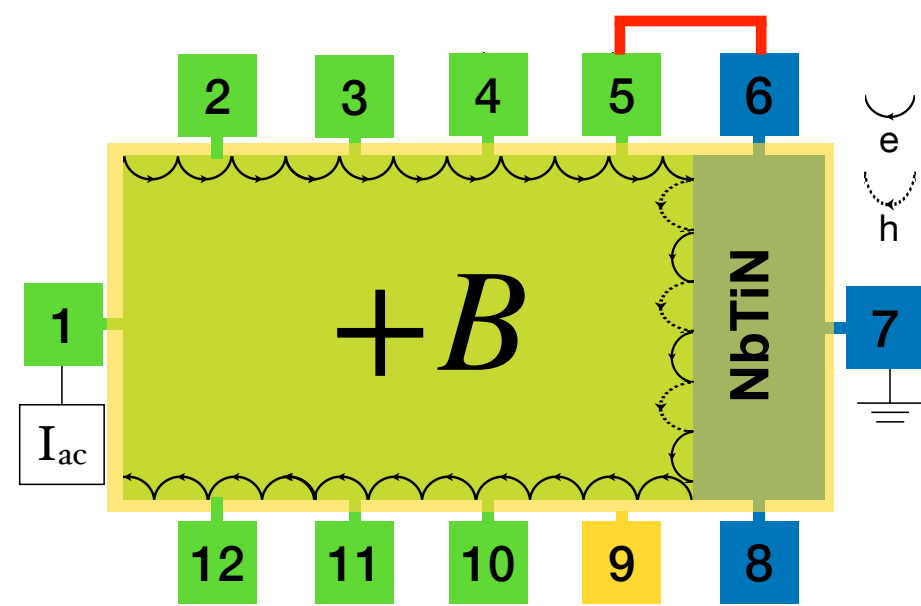


$$R_{5-6} = 0$$

$$R_{5-6} = R_{Hall}$$

Superconductor?

Interface(2DEG/Superconductor) resistance



Normal

$$R_{5-6} = \frac{h}{e^2} \frac{R}{NT}$$

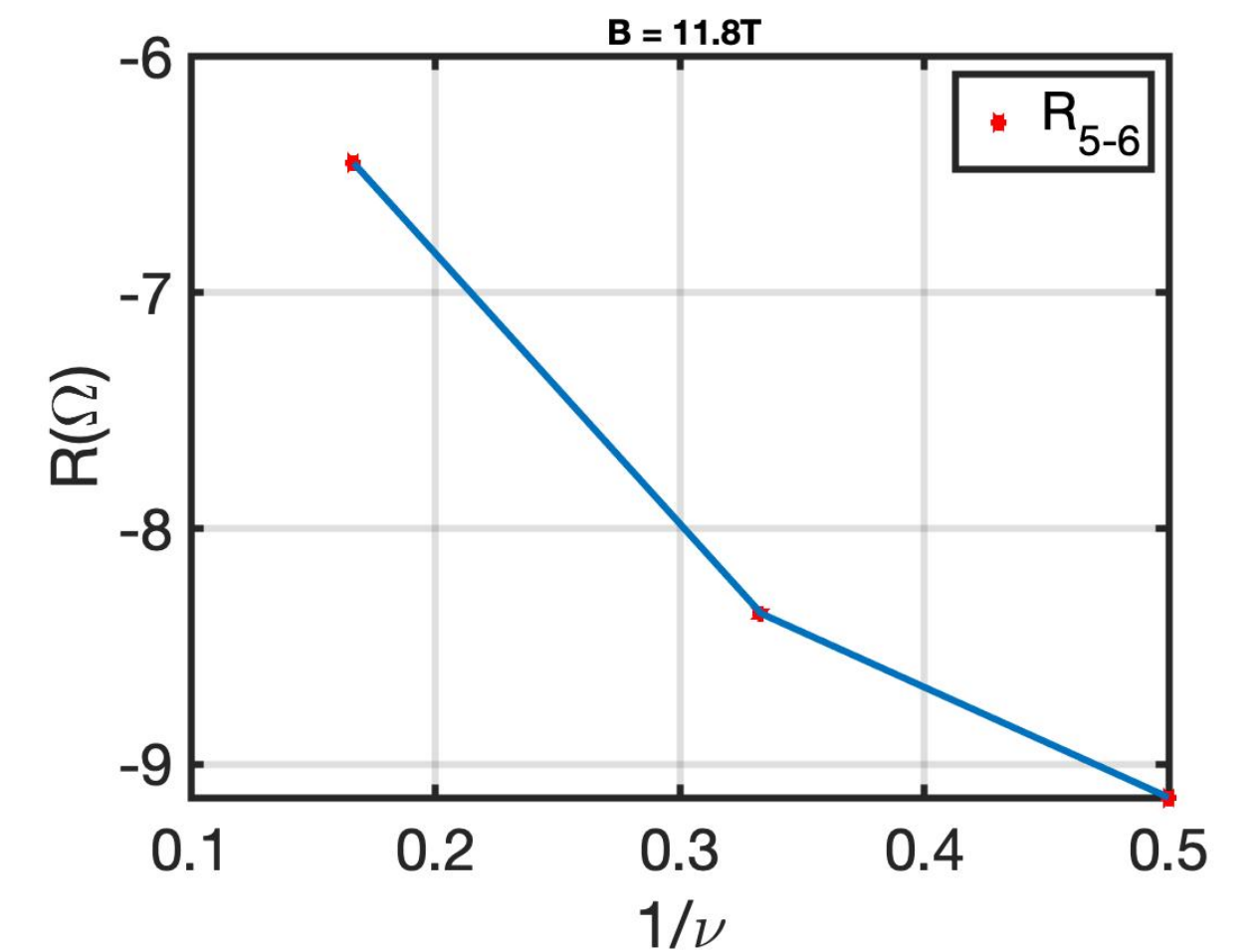
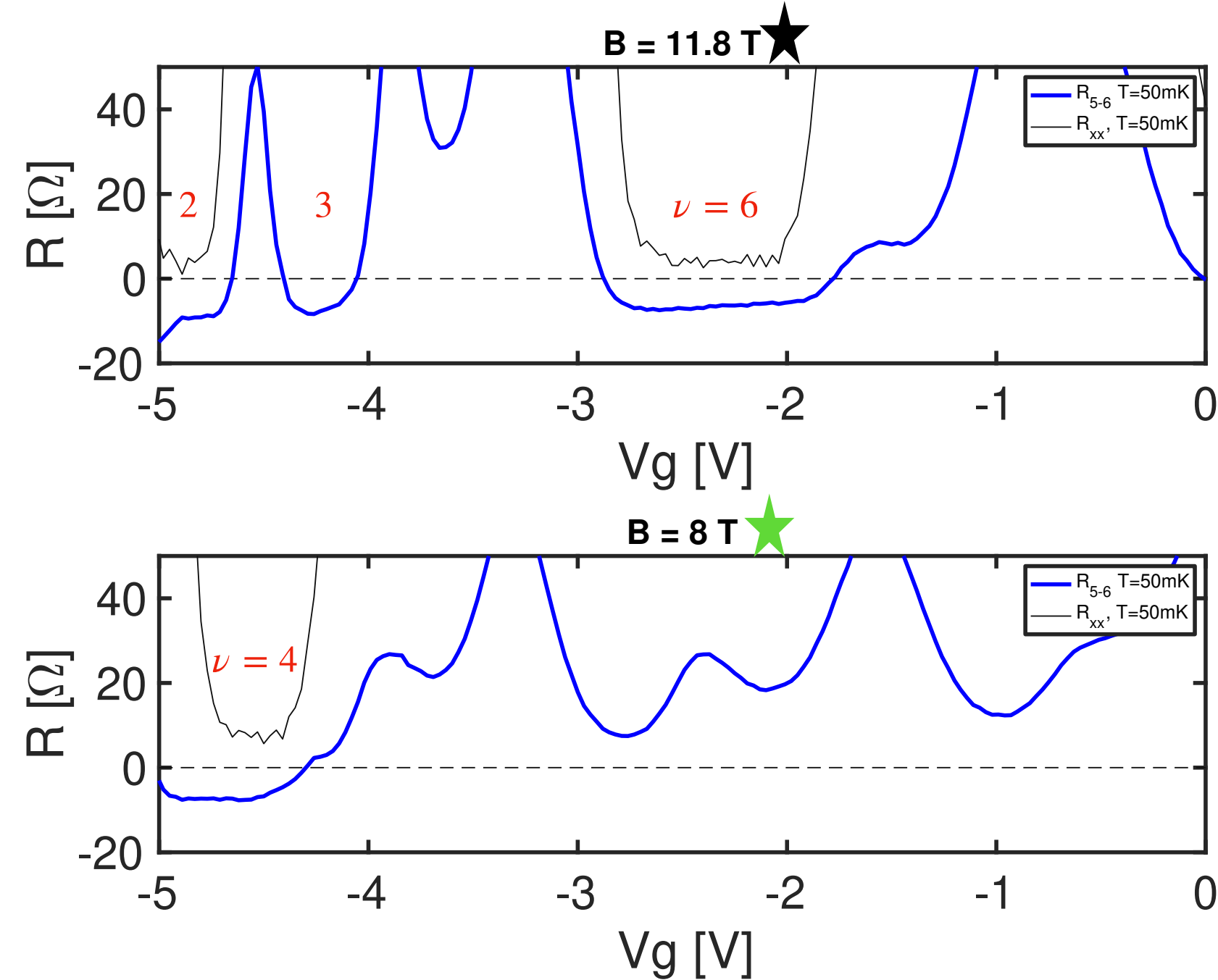
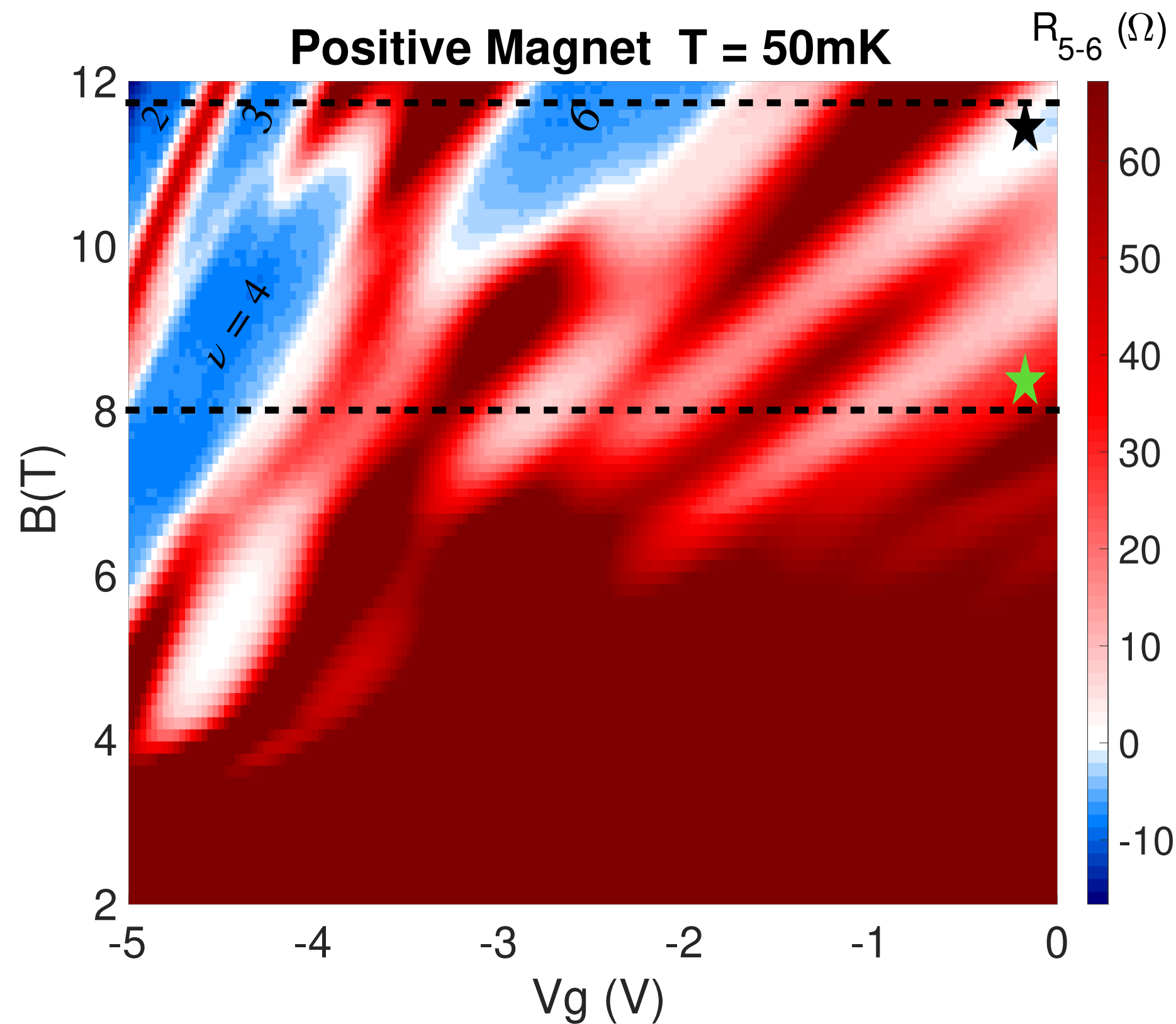
Superconductor

$$R_{5-6} = \frac{h}{e^2} \frac{R - A}{N(T + A)}$$

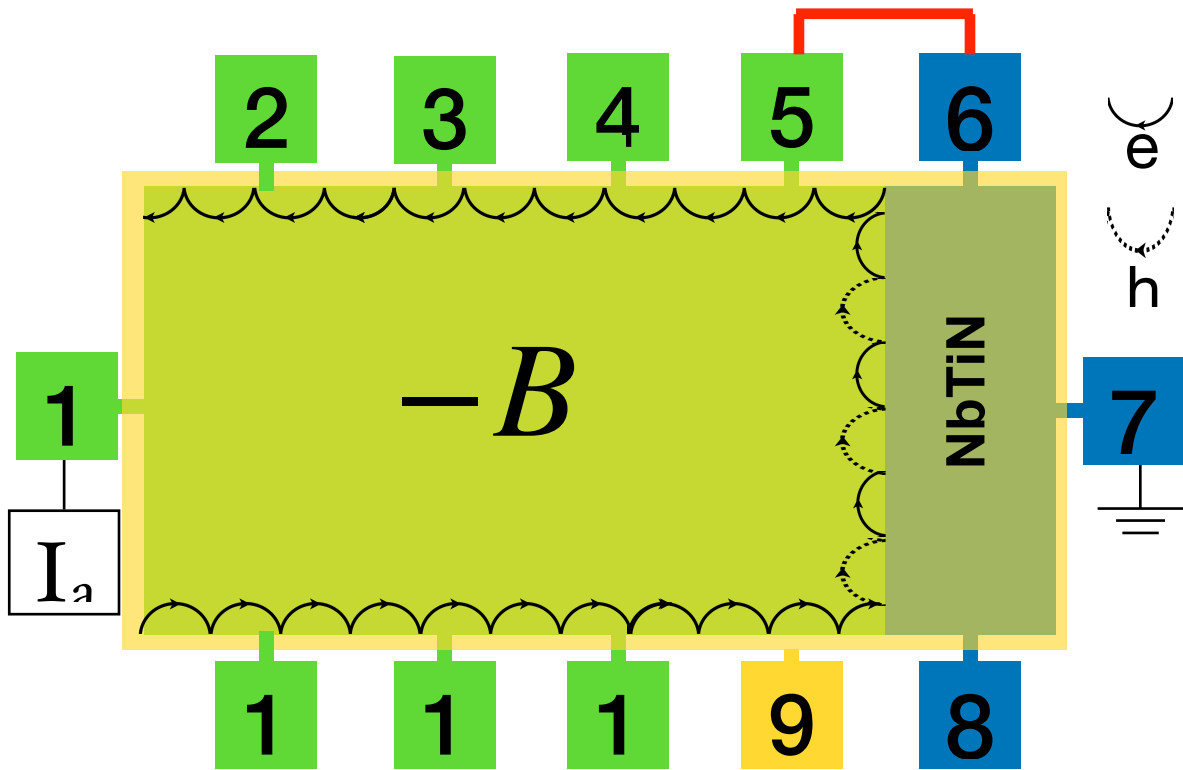
If $A > 0 \rightarrow R_{5-6} < 0$

Ideal interface: $A = 1$

(A: andreev reflection contribution)



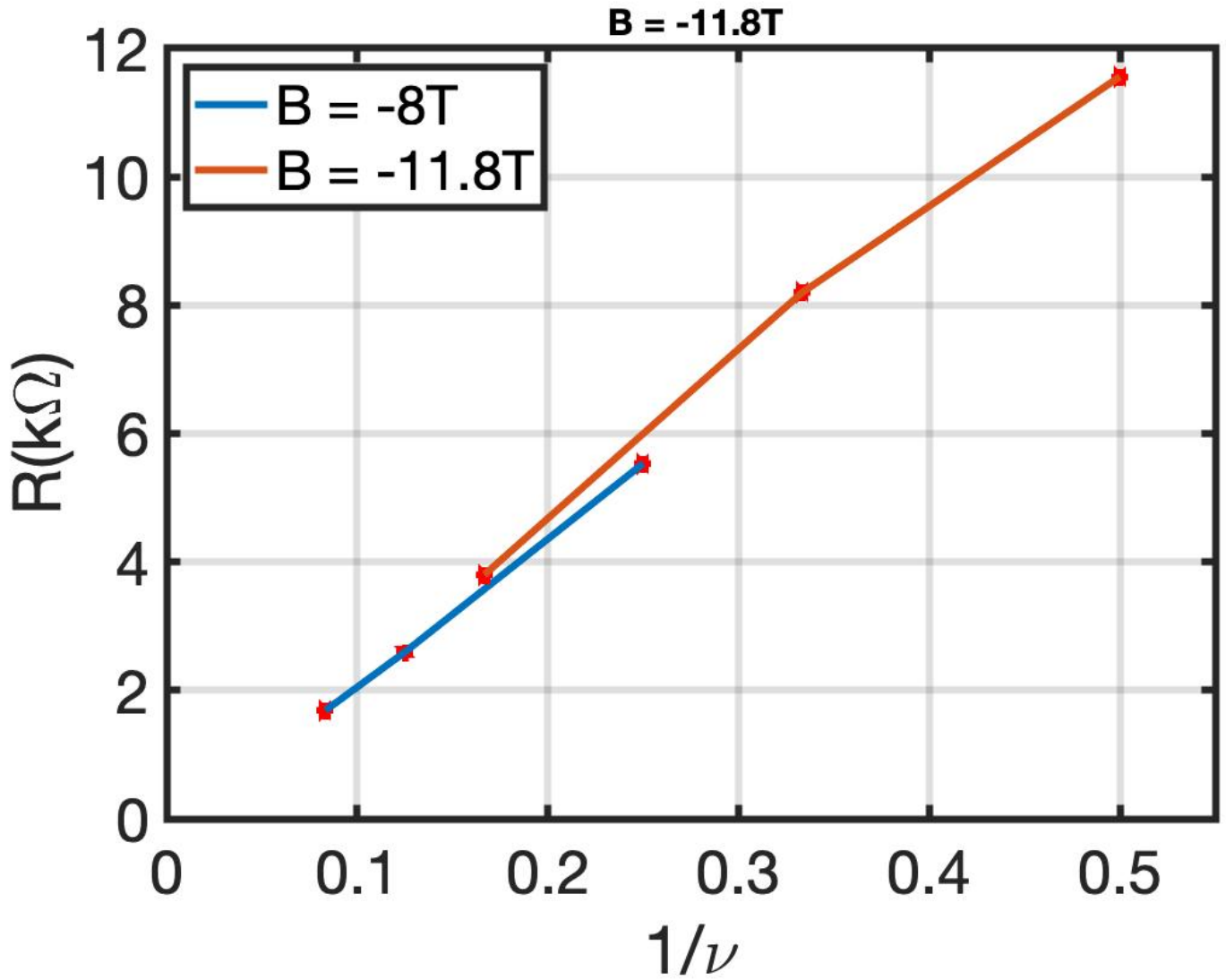
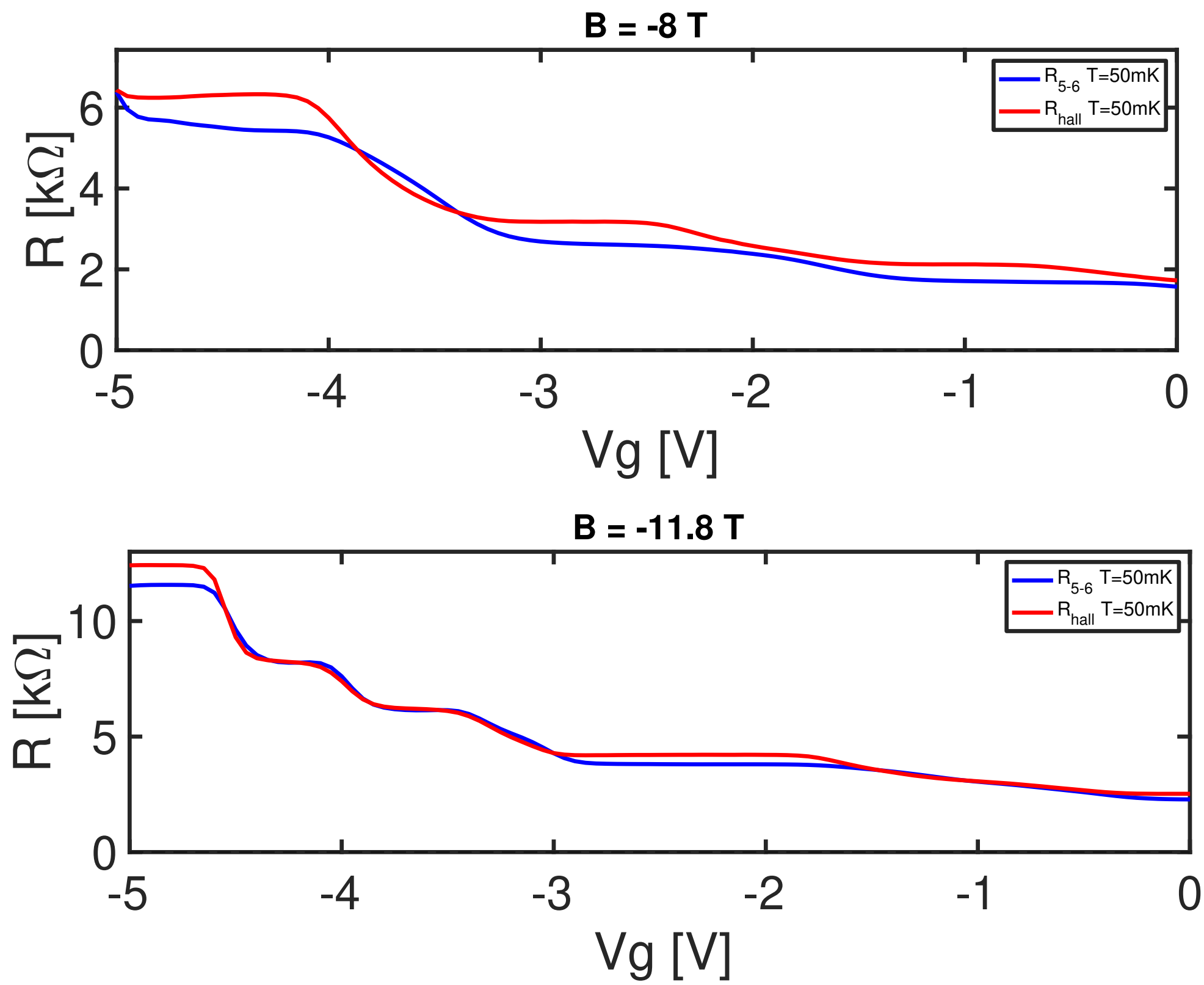
$$\frac{R - A}{(T + A)} = -3.2 \times 10^{-4}$$



Normal $R_{5-6} = \frac{h}{e^2} \frac{1}{NT}$ $\rightarrow$ Superconductor $R_{5-6} = \frac{h}{e^2} \frac{1}{N(T+A)}$

(A: andreev reflection contribution)

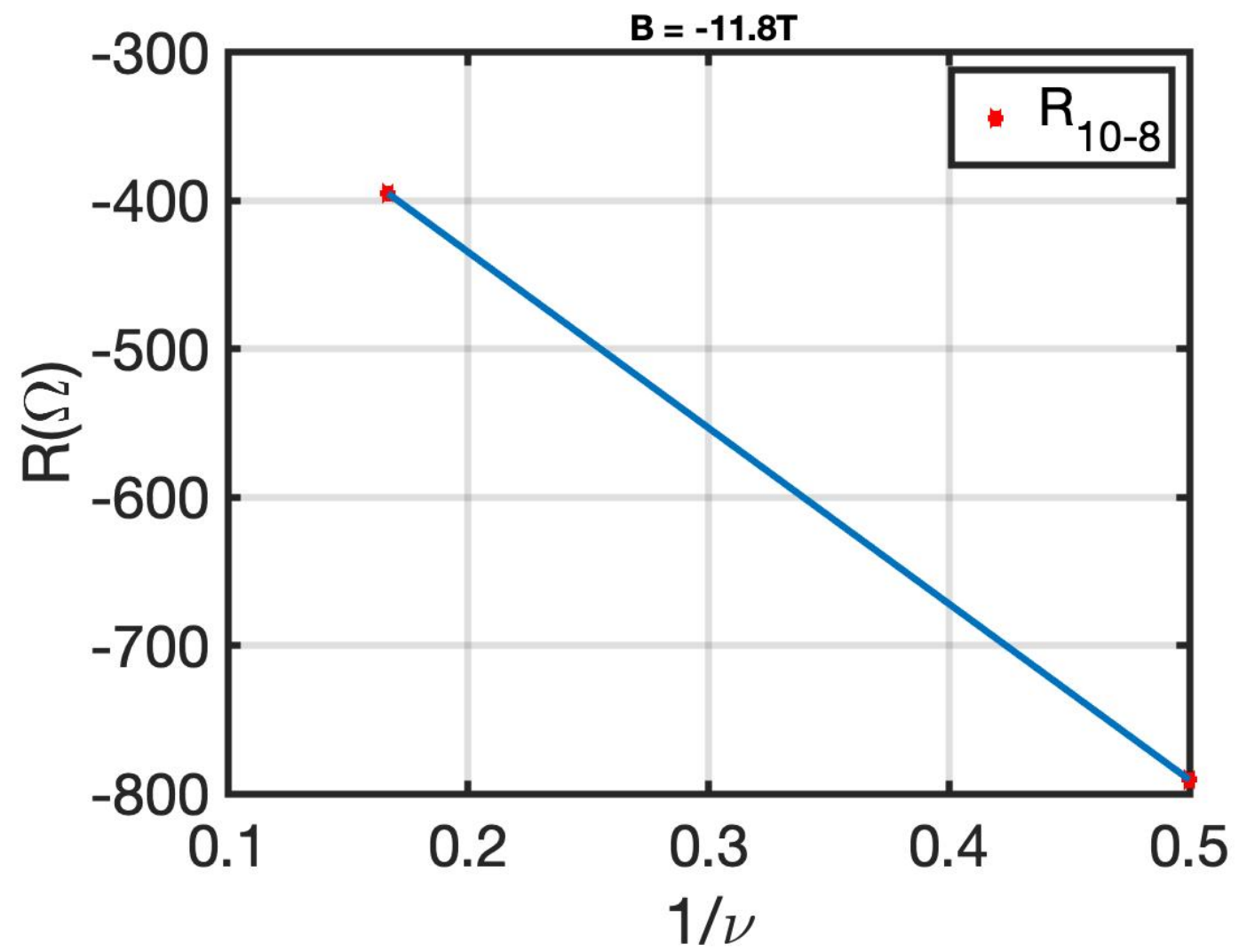
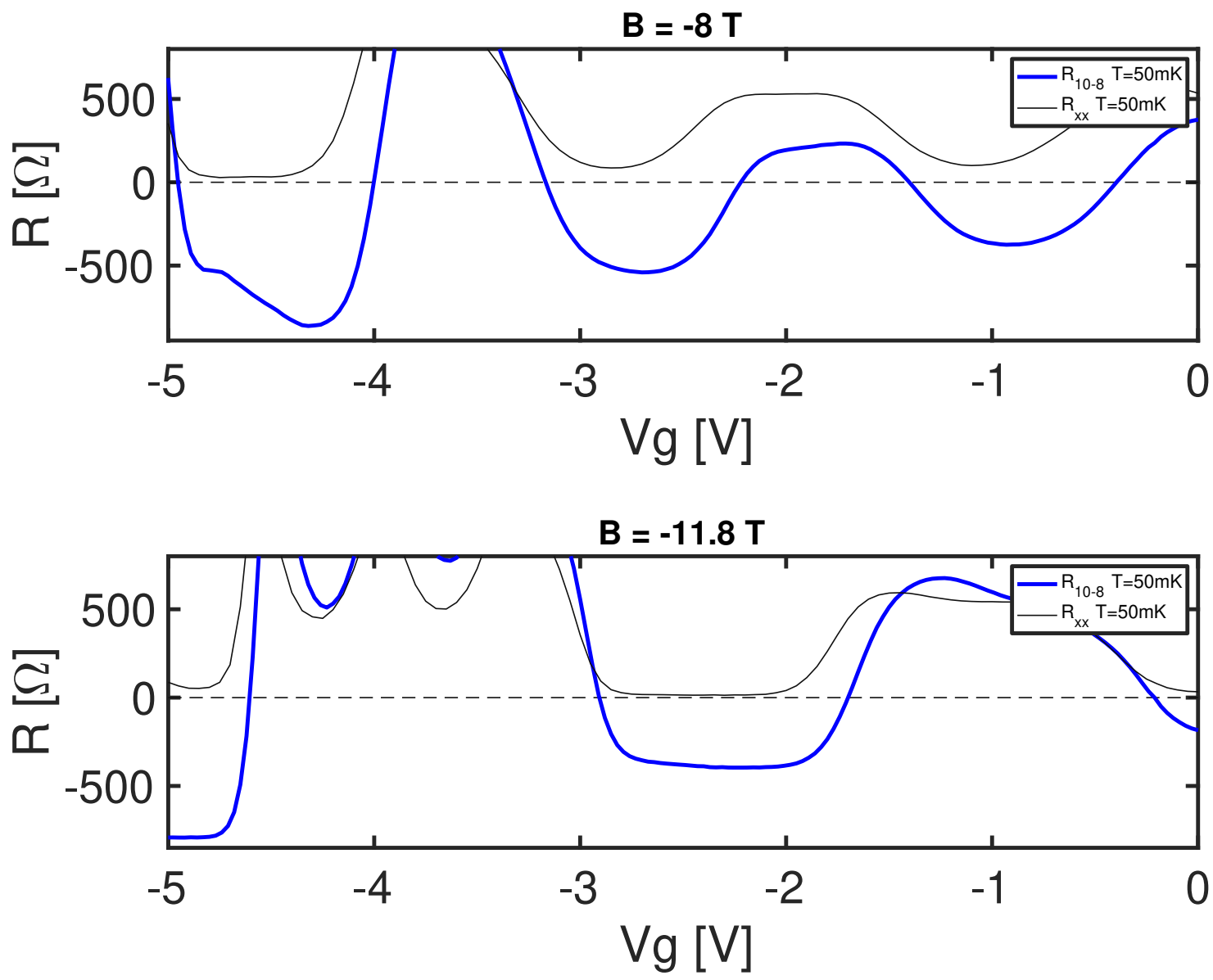
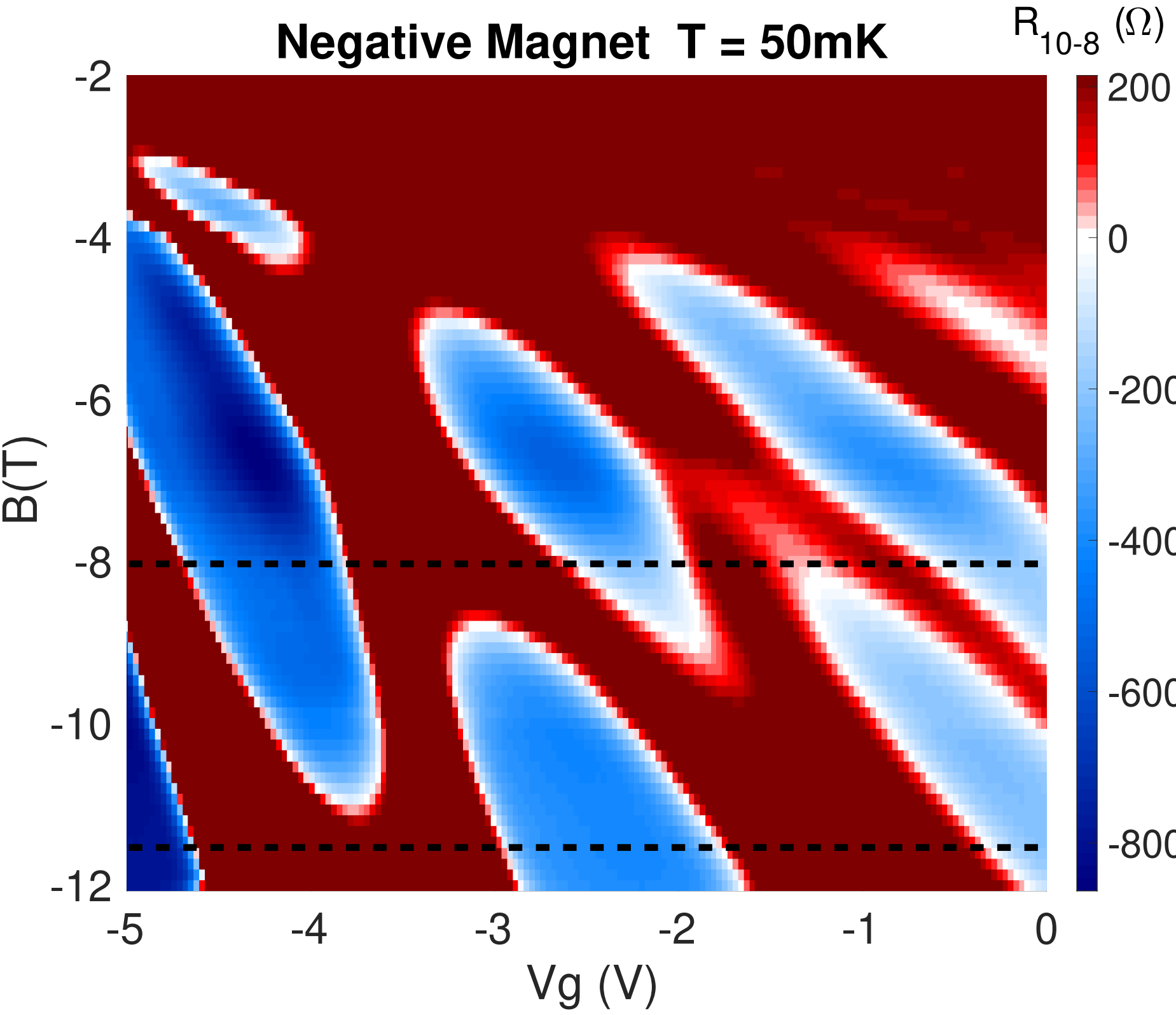
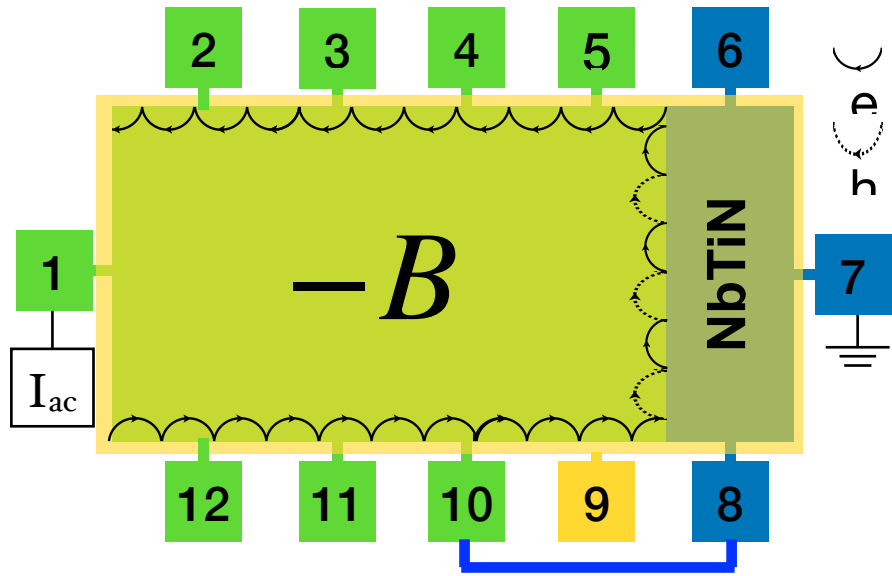
If $A > 0 \rightarrow R_{5-6} < R_{Hall}$



From -11.8T : $T + A = 1.1088$

From -8T : $T + A = 1.1136$

Interface resistance



$$\frac{R - A}{(T + A)} = -0.04$$

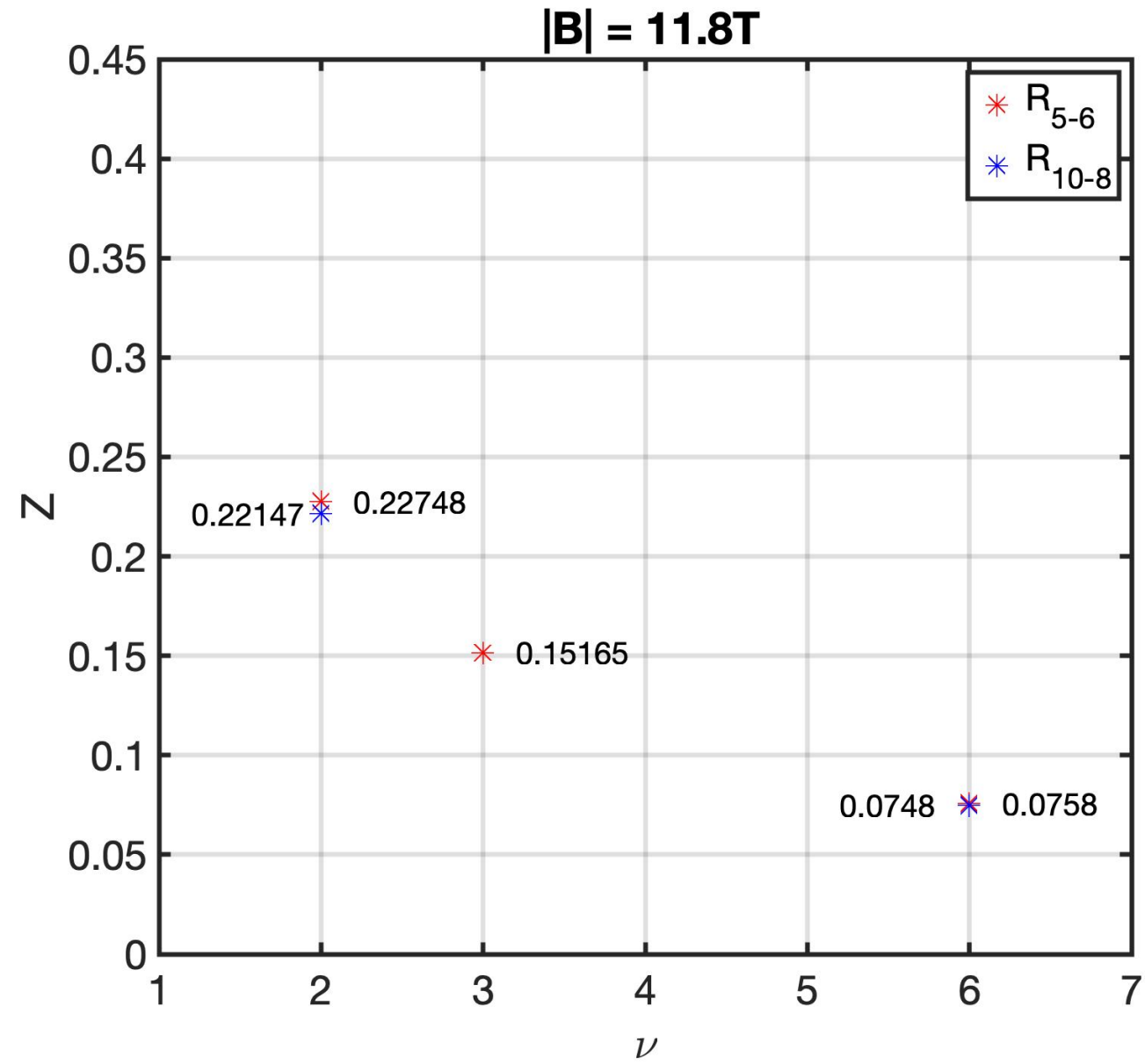
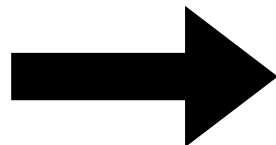
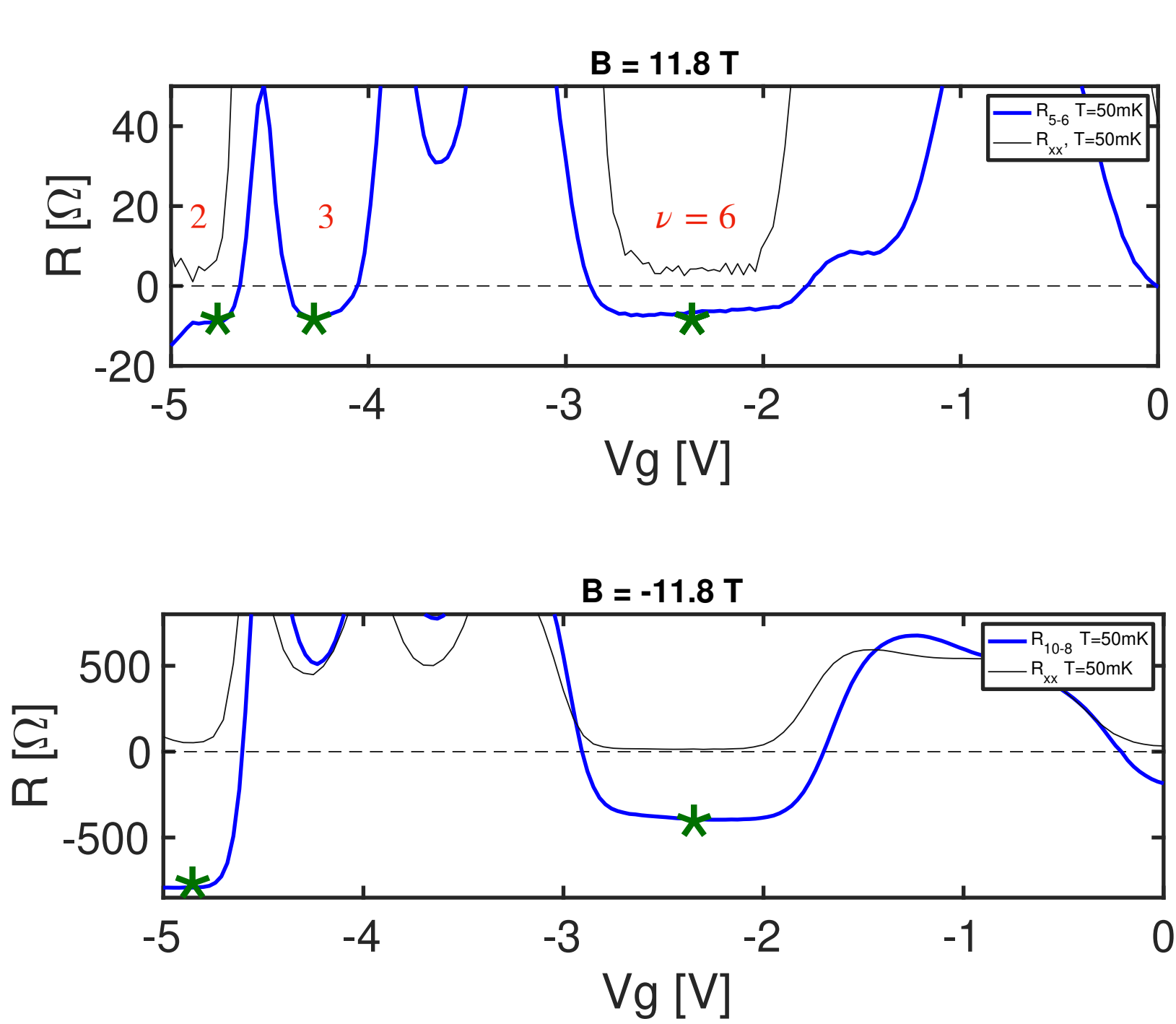
Z calculation

$$R_{5-6 \text{ or } 10-8} = \frac{h}{2\nu e^2} ((1 + 2Z^2)^2 - 2)$$

Ideal interface: $Z = 0$

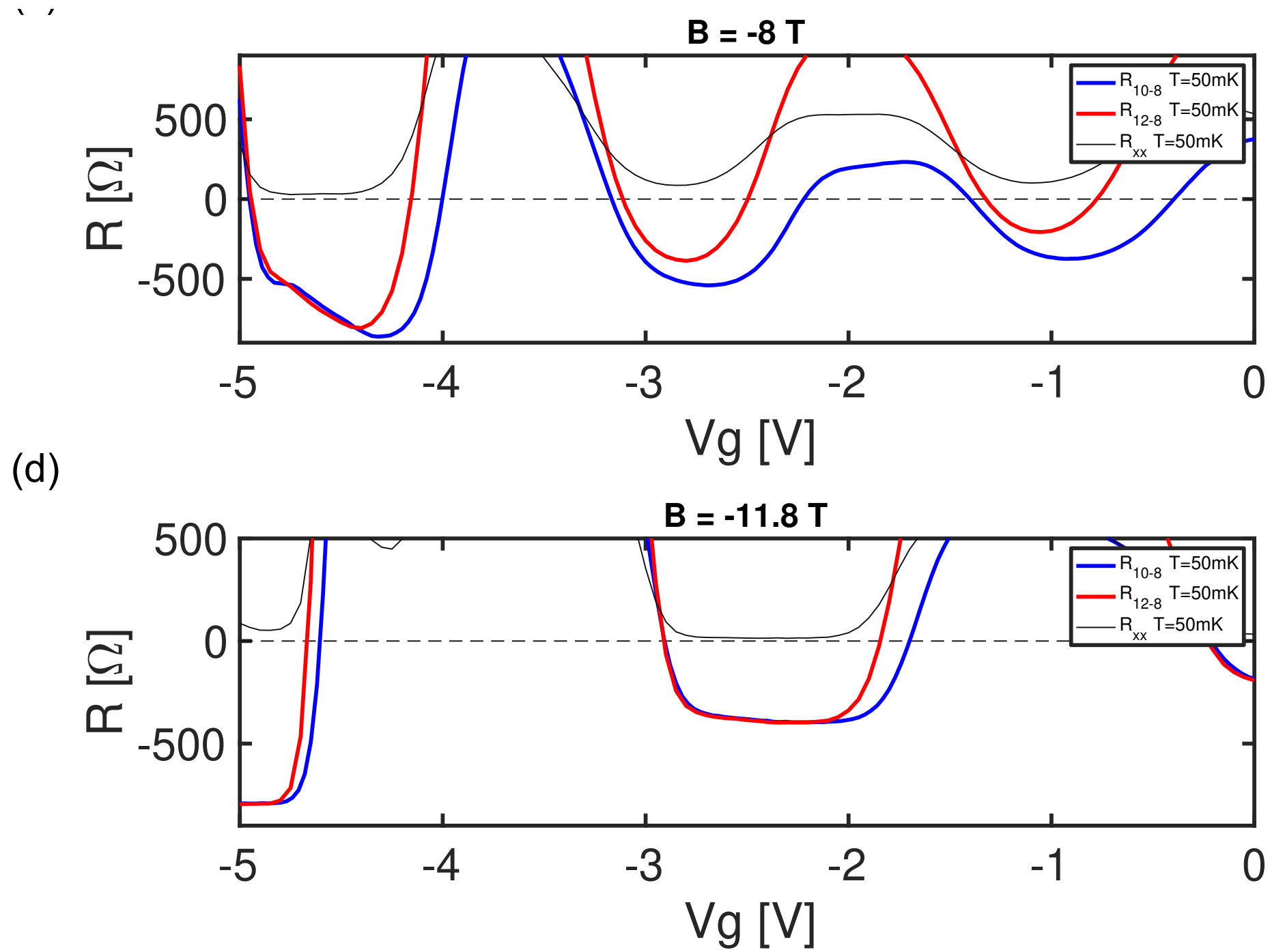
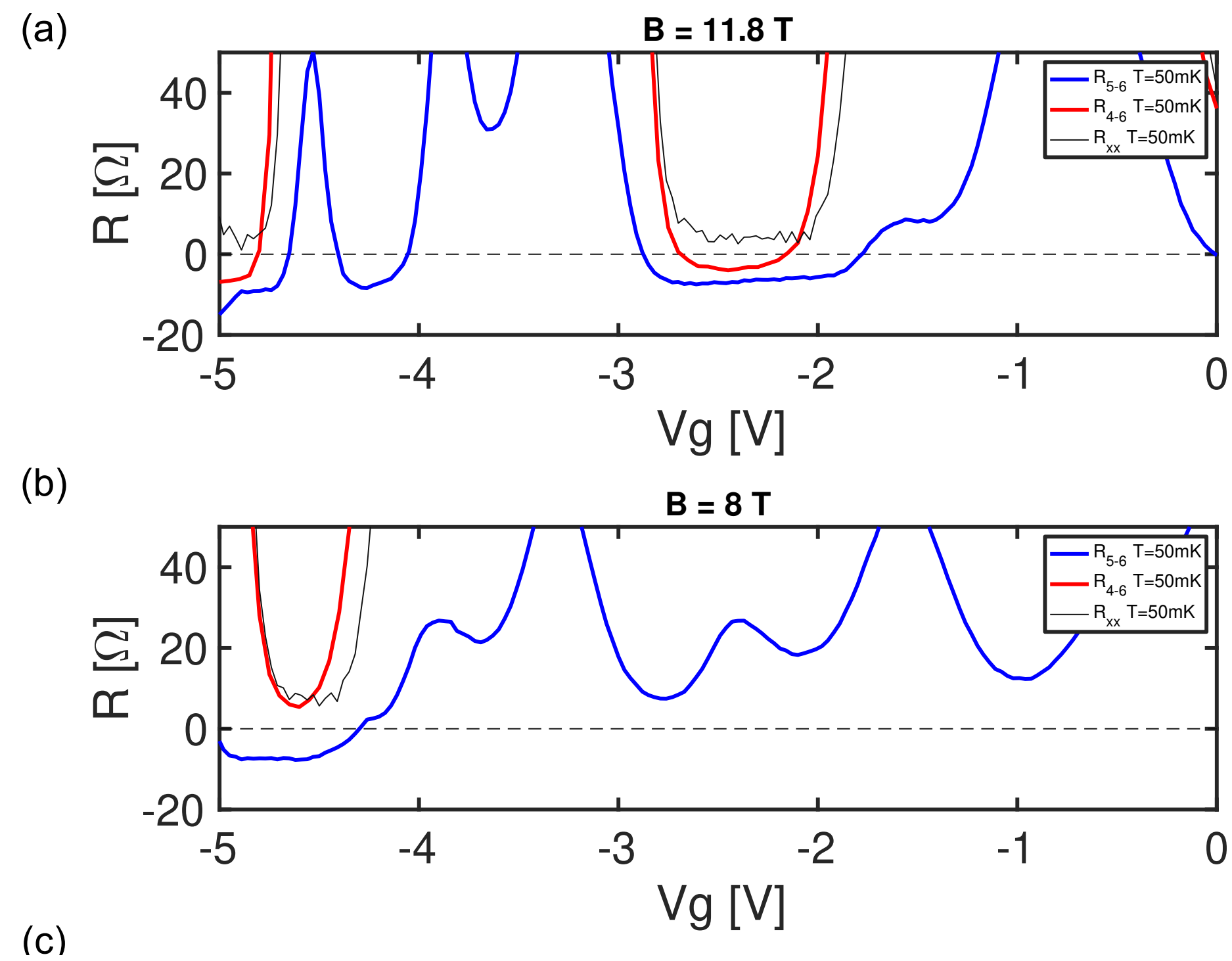
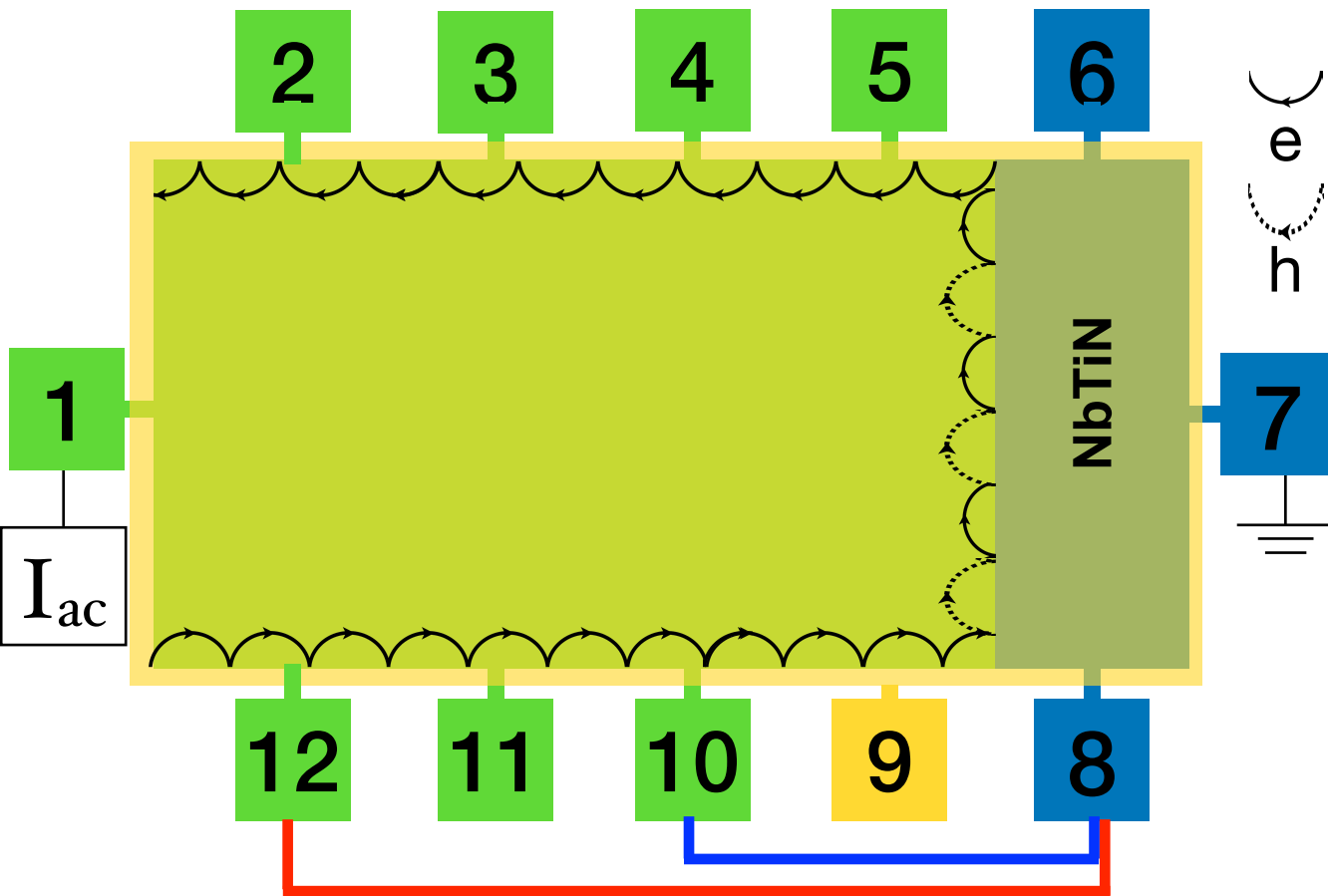
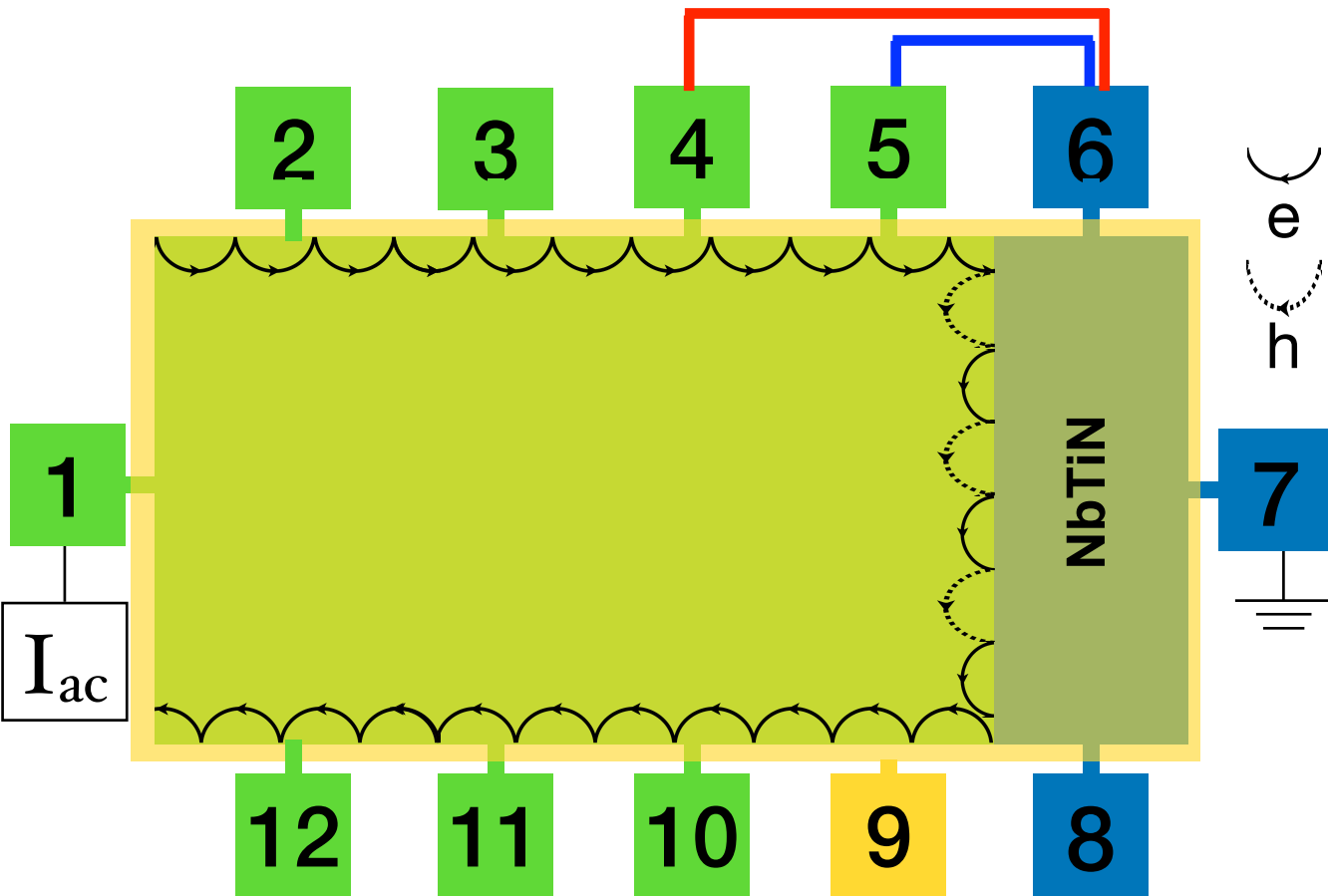
$Z_c = 0.45$

If $0 < Z < Z_c = 0.45 \rightarrow R_{5-6} < 0$



$0.075 < Z < 0.227$

Distance dependence of interface resistance



- Fabrication of gate controlled InAs/NbTiN Hall-bar
- Negative resistance observation at 2DEG/Superconductor interface in IQHS
- Andreev reflection at 2DEG/Superconductor interface up to ~10%



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This work was performed, in part, at the Center for Integrated Nanotechnologies, a U.S.~DOE, Office of BESs, user facility.

This paper describes objective technical results and analysis.

Any subjective views or opinions that might be expressed in the paper do not necessarily represent the views of the U.S. DOE or the United States Government.